



# **COMP.CE.510**

# **Chip Implementation**

***Lecture Starts. 14.15***

# Introduction- Chip Implementation

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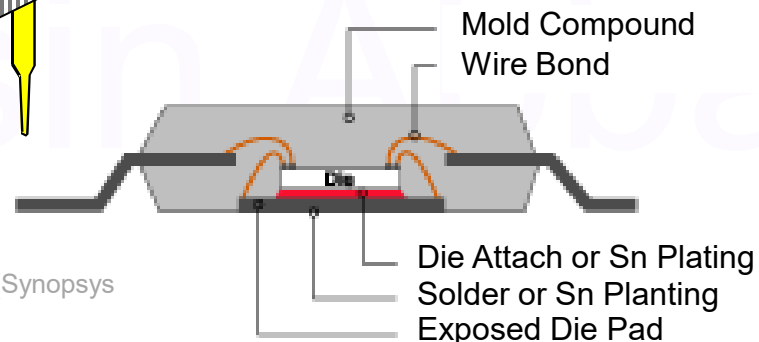
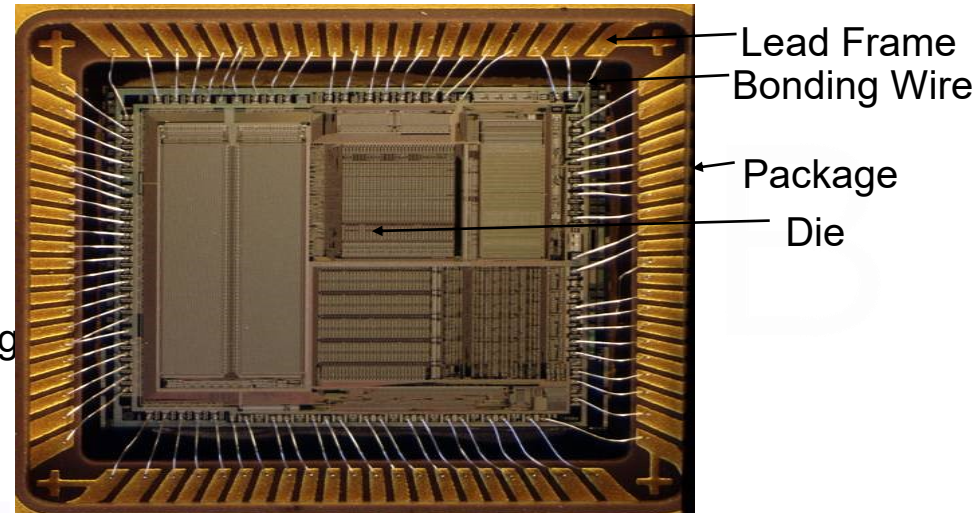
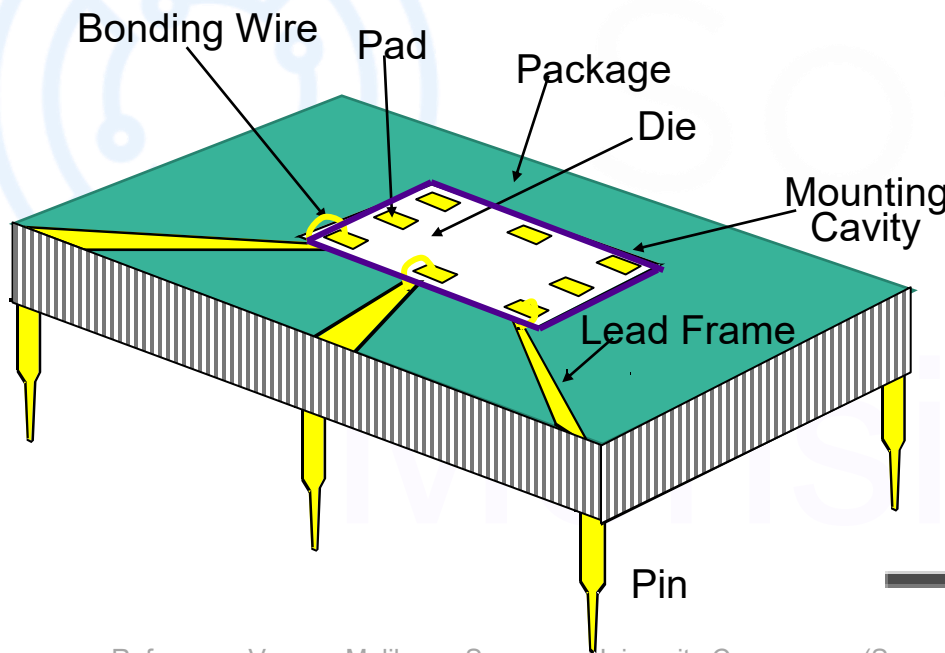
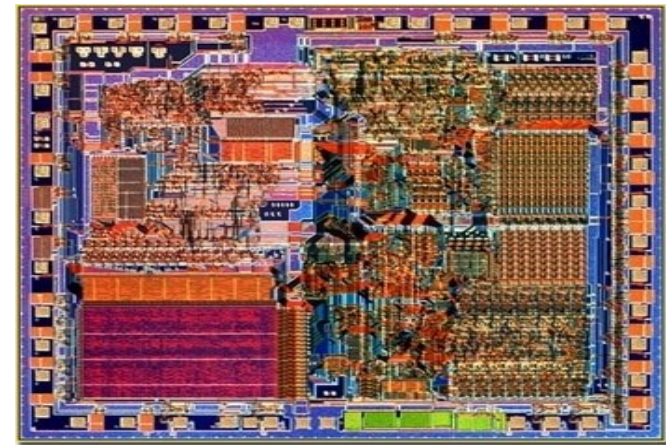
# Semiconductor Chips

- Semiconductor chips are used everywhere:
  - Computers
  - Cellular phones
  - Tablets
  - Gaming systems
  - DVD players, TVs
  - Watches
  - Cars
  - Medical devices
  - Pacemakers and coffee pots
  - Space stations
  - Greeting cards



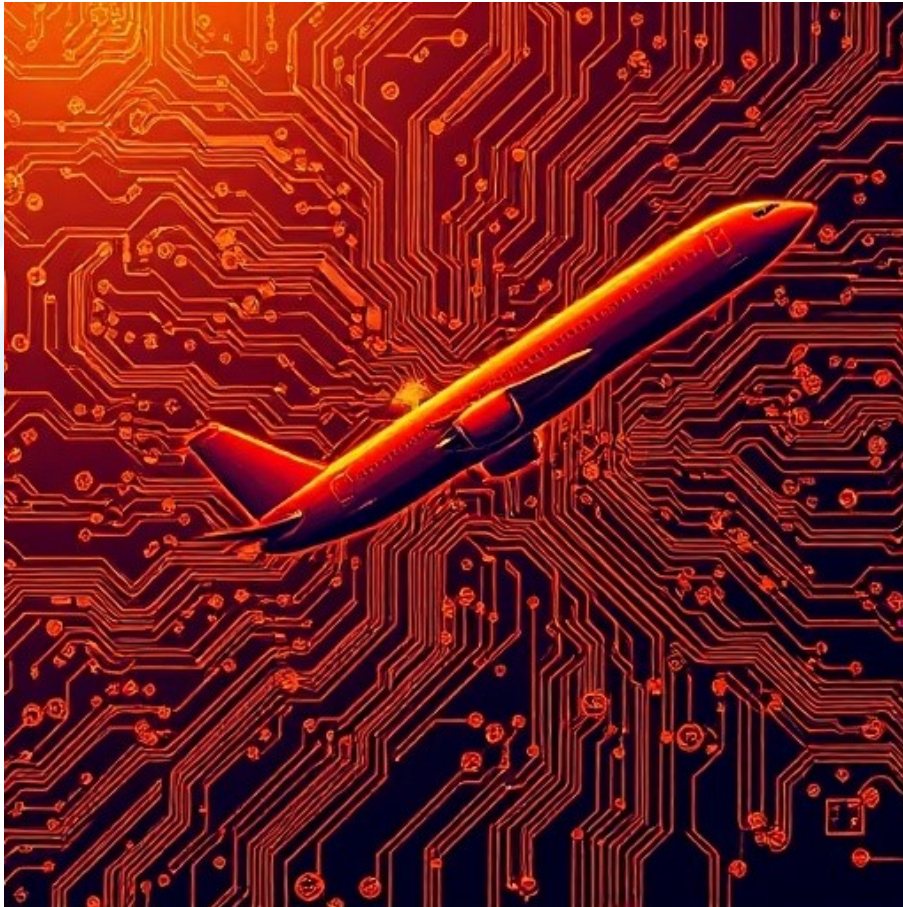
# Semiconductor Chips

- Integrated circuits (IC) is a complex set of electronic components, and their interconnections etched on a chip.





# IC Design/Chip Implementation **is as easy as flying a plane.....**



# Course Contents

- **Lecture 1:** Introduction- Chip Implementation
- **Lecture 2: RTL-to-GDSII The Bare Minimum**
  - **Also Serves as LAB 1**
- **Lecture 3:** Static Timing Analysis (STA)
- **Lecture 4:** Logical Synthesis
- **Lecture 5:** Logical Synthesis- Optimization and DFT
- **Lecture 6:** To Physical Domain-Floor Planning
- **Lecture 7:** Placement
- **Lecture 8:** Clock Tree Synthesis (CTS)
- **Lecture 9:** Routing
- **Lecture 10:** Chip Finishing
- **Lecture 11:** I/O Cells and Packaging
- **Lecture 12:** Low Power Design and Fabrication Process Flow



# Lab Sessions

1. Introduction to design flow (From 11<sup>th</sup> Sep.)

2. Static Timing Analysis

3. Logical Synthesis

4. Scan insertion + ATPG

5. Formal Verification

6. Floorplanning I

7. Floorplanning II

8. Clock Tree Synthesis

9. DRC & LVS

10. Competition

**Have to sign NDA**

## Teachers

- Syed Mohsin Abbas
- **Tero Lehtinen**
- Matti Käyrä
- Arto Oinonen



**Thursday and Friday  
14.00–16.00 (TC217)**

## Competition (10 Points)

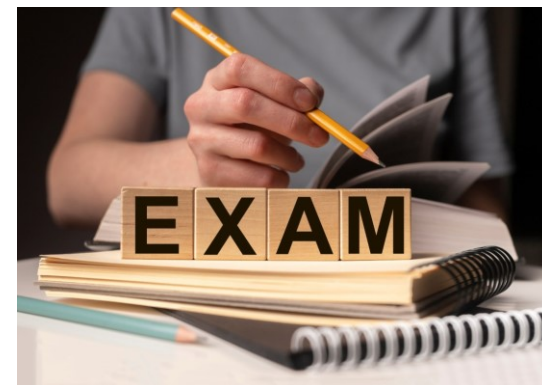
Given RTL, students need to run full flow RTL2GDSII - flow using it. They “compete” against a reference implementation. Points will be awarded for:

- Area
- Max clock frequency
- Total power consumption (vcd/activity file will be provided)
- Test coverage
- Flow run-time

Design will have to pass all checks: timing needs to be clean, DRC & LVS ok, formal verification ok, test coverage > 98%

# Exam and Grading

- Grading Criterion (100 Points)
  - 45 points Electronic exam (From lectures)
  - 45 points Lab Sessions
    - 5 points/Lab (Lab. 1 – 9)
  - 10 points for competition
- Grades (1-5)
  - Grade 5 (90+ points)
  - Grade 4 (80+ points)
  - Grade 3 (70+ points)
  - Grade 2 (60+ points)
  - Grade 1 (50+ points)



## Passing points (50)

- Atleast 6 labs (30 points)
- Atleast 20+ marks in Exam.

Mattermost registration:

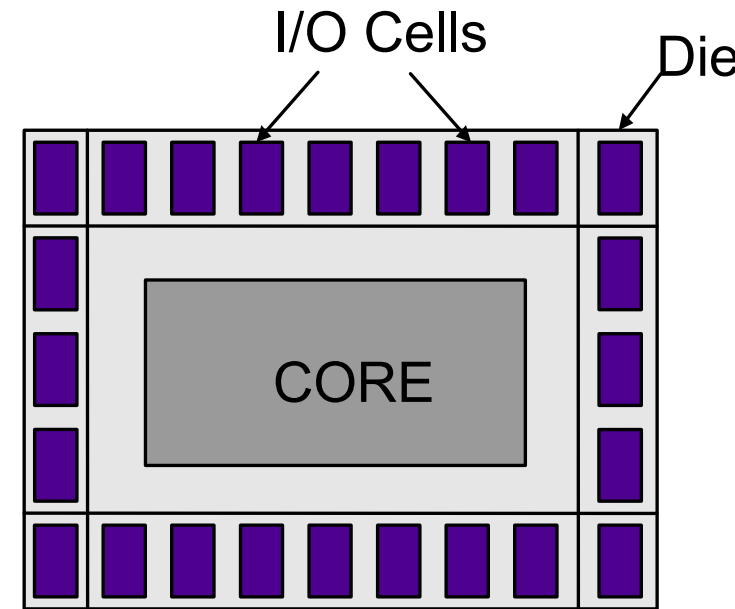
[https://mattermost.tut.fi/signup\\_user\\_complete/?id=yf3x7e9xo3f4jy5um9pyr9a35y](https://mattermost.tut.fi/signup_user_complete/?id=yf3x7e9xo3f4jy5um9pyr9a35y)

Course channel: <https://mattermost.tut.fi/studentsetstaff/channels/compce510>

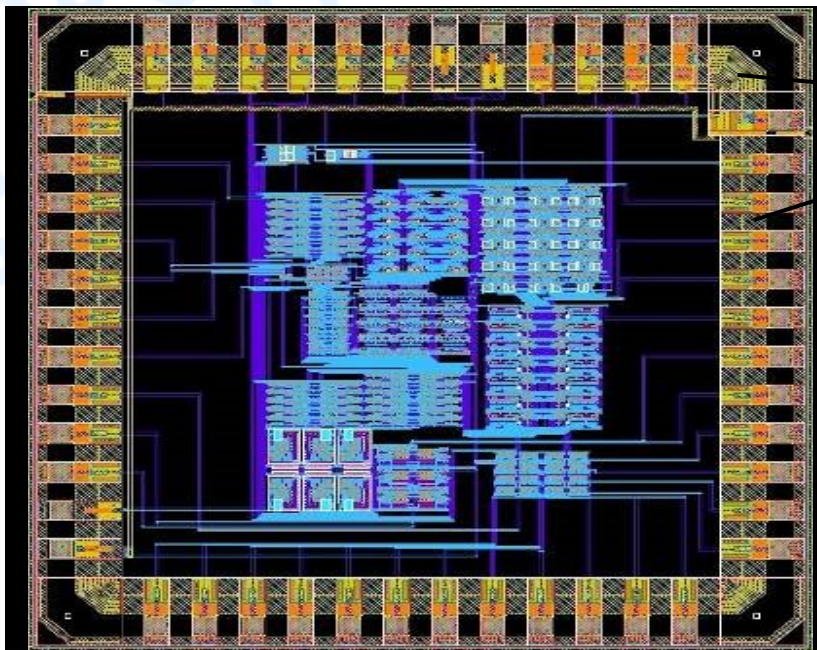


# IC Structure: Core, IO Cells

**Core** - provides basic functionality of IC



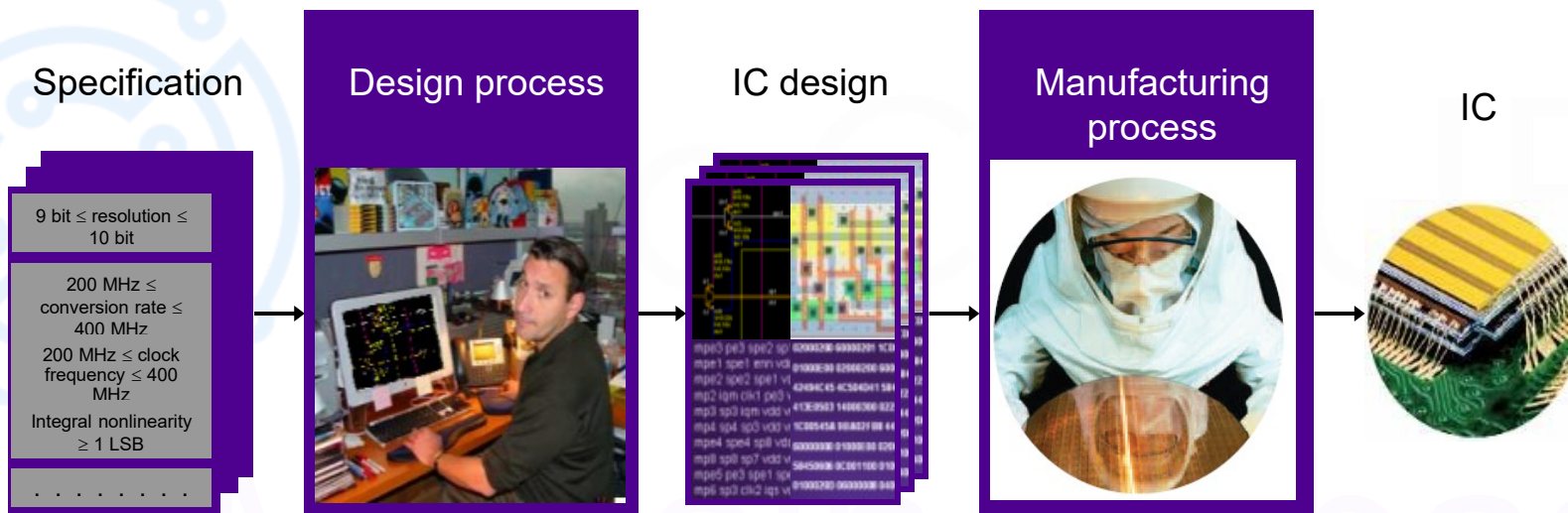
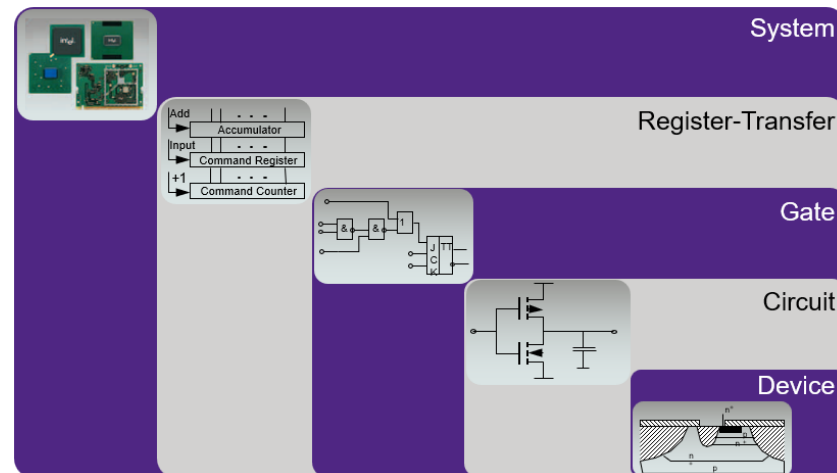
Surrounding Environment



IO Ring

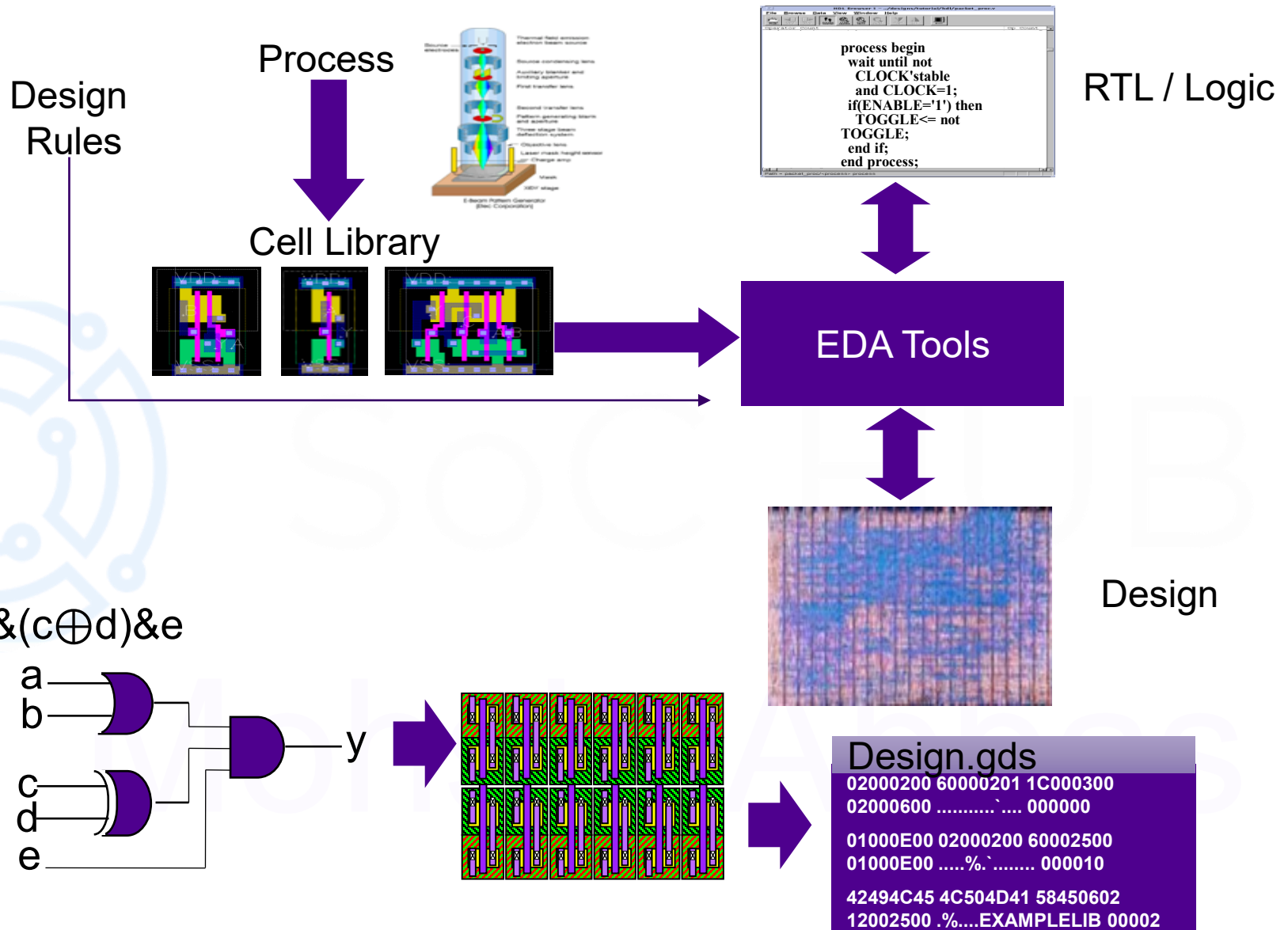
**I/O Cell** – provides accordance between the Core and surrounding environment (voltage levels, signal transfer velocity, resistances, etc).

# Phases of IC Design



Design process is the process of getting IC design from specification

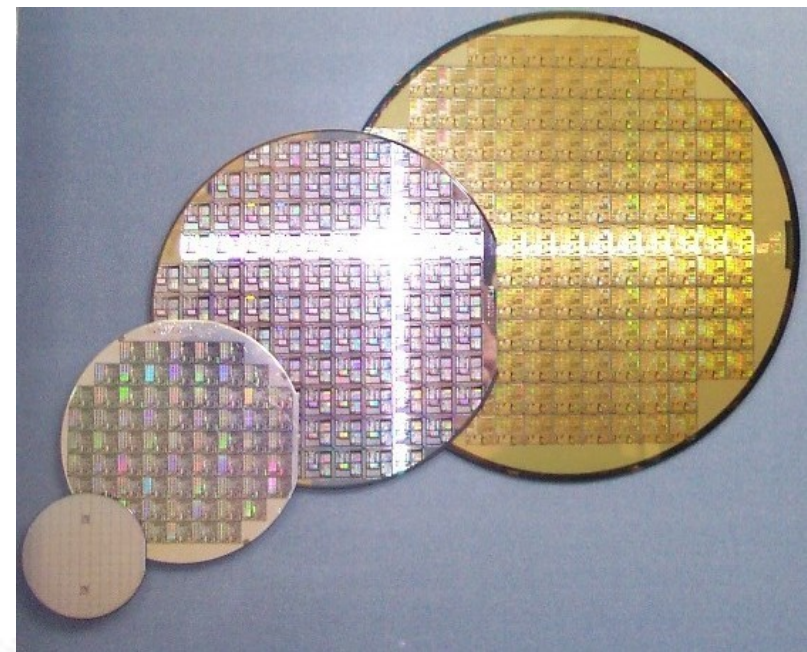
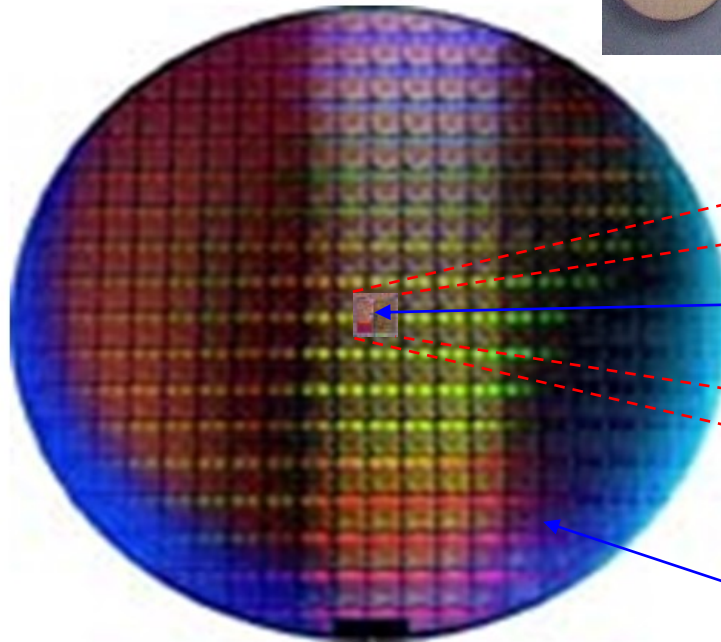
# Digital Design Flow



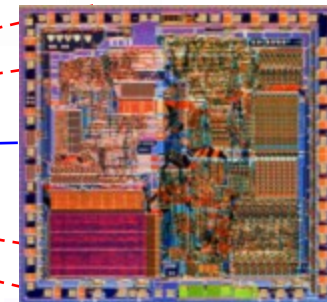
# Wafer and Die

- ICs are fabricated on circular slices of silicon called wafers.
  - Wafer contains various identical dies.

Side view of a Wafer



Die



Top view of a die

Wafer



# Wafer

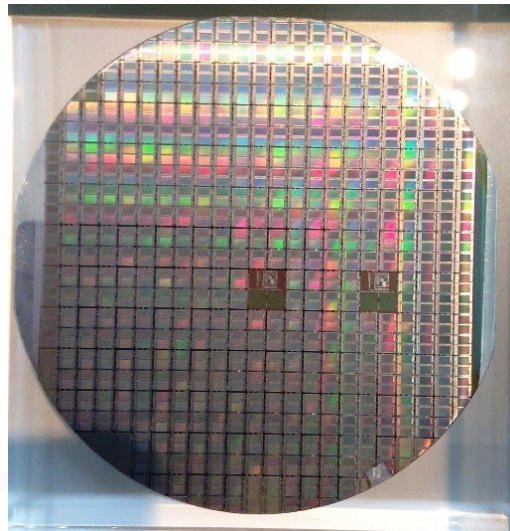
- Wafer is cut from metal-cast of single crystal silicon





# Wafer

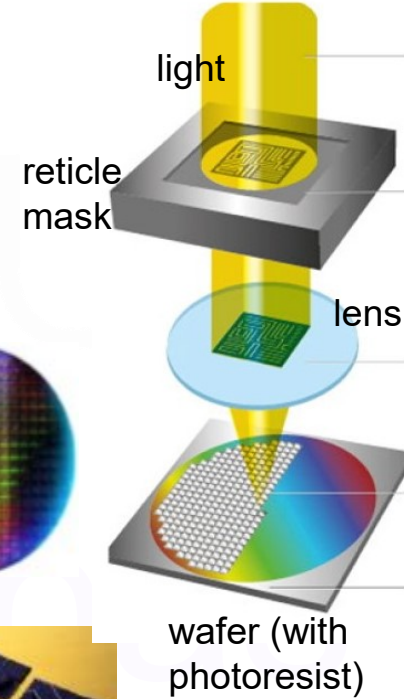
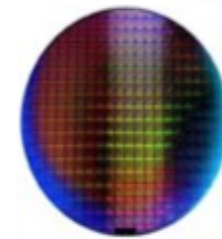
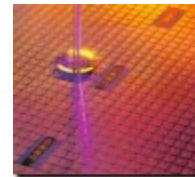
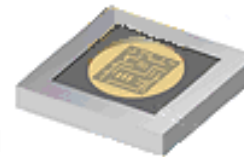
- Wafer is cut from metal-cast of single crystal silicon



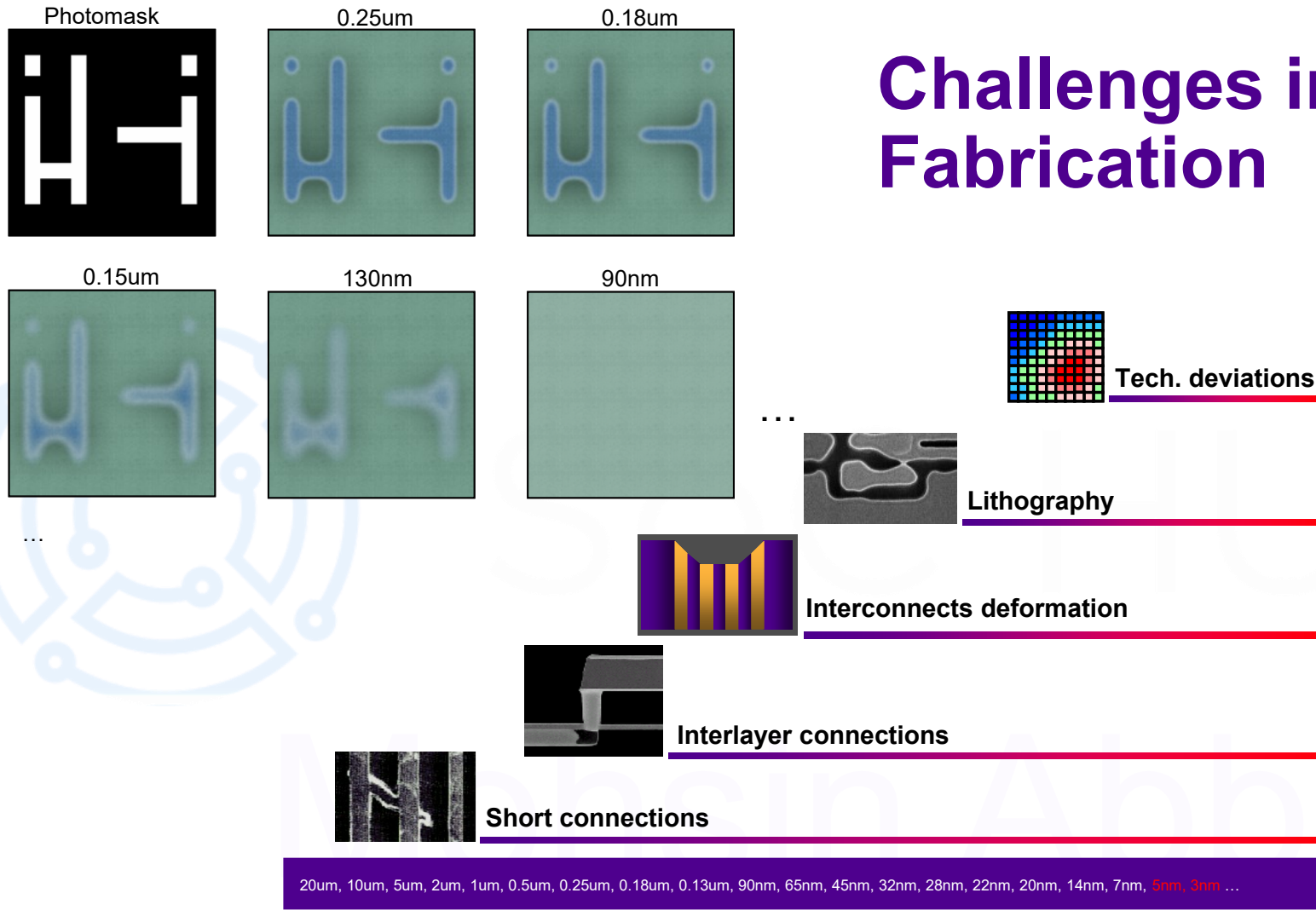
# IC Fabrication- Simplified

The series of steps used to create integrated circuits is called the semiconductor fabrication process.

1. Growing of a giant crystal of silicon
2. Slicing it up into round wafers and polish them.
3. Coating of a wafer with a photographic chemical that hardens when exposed to light (**Photoresist Coating**)
4. Taking a picture of a pattern to embed in the silicon (**Photolithography**).
5. Shrinking of the picture and shining a light through it (**Exposure**)
6. Dipping of the wafer in acid (**Etching**)
7. Repetition of steps 3 - 6 many times, producing layers of patterns etched into the wafer (**Metal layer deposition**)
8. Slicing up the wafer into many rectangle chips.
9. IC Packaging
10. IC Testing
11. PCB Mounting



# Challenges in IC Fabrication



# Largest IC Foundries



TSMC

Taiwan Semiconductor Manufacturing Company



GF

Global Foundries



UMC

United Microelectronics Corporation  
Samsung



SMIC

Semiconductor Manufacturing International Corporation



TowerJazz

Tower Semiconductor



ELMOS

Elmos Semiconductor AG



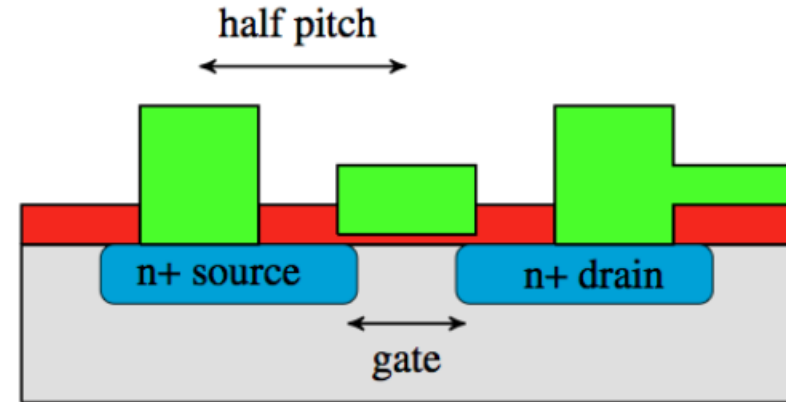
XFAB

Mixed-Signal Foundry Expert

# Process/Technology Nodes

**Technology node** - concerns to a specific semiconductor process and its design rules.

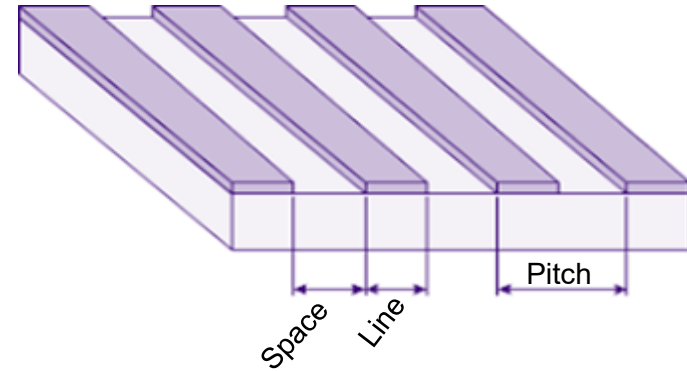
- The smaller technology node means the smaller feature size.
  - Gate length and metal1(M1) half-pitch.
- Recent technology nodes such as 22nm, 16nm, 14nm, and 10nm refer to a specific generation of chips and does not correspond to any geometric parameter.



For example, in 2005, the node on an Intel microprocessor was 65nm, the gate width was 32nm, but the half pitch was 105nm.



# Process/Technology Nodes



Example processes. Each has its own design rules.

TSMC 22nm G Logic 1.0V/3.3V  
 SMIC 45nm LL Logic 1.2V/3.3V  
 SMIC 45nm LV Logic 1.0V/3.3V  
 Samsung 32nm LP Logic 1.2V/3.3V  
 UMC 32nm LL Logic 1.2V/2.5V  
 Samsung 14nm LP Logic 0.8V/1.5V  
 UMC 14nm LL Logic 0.8V/1.8V

G – generic  
 LL – low leakage  
 LV – low voltage  
 LP – low power

Design Rules - Rules constructed to ensure that design works even when small fabrication errors occur

min. spacing



min. width rule

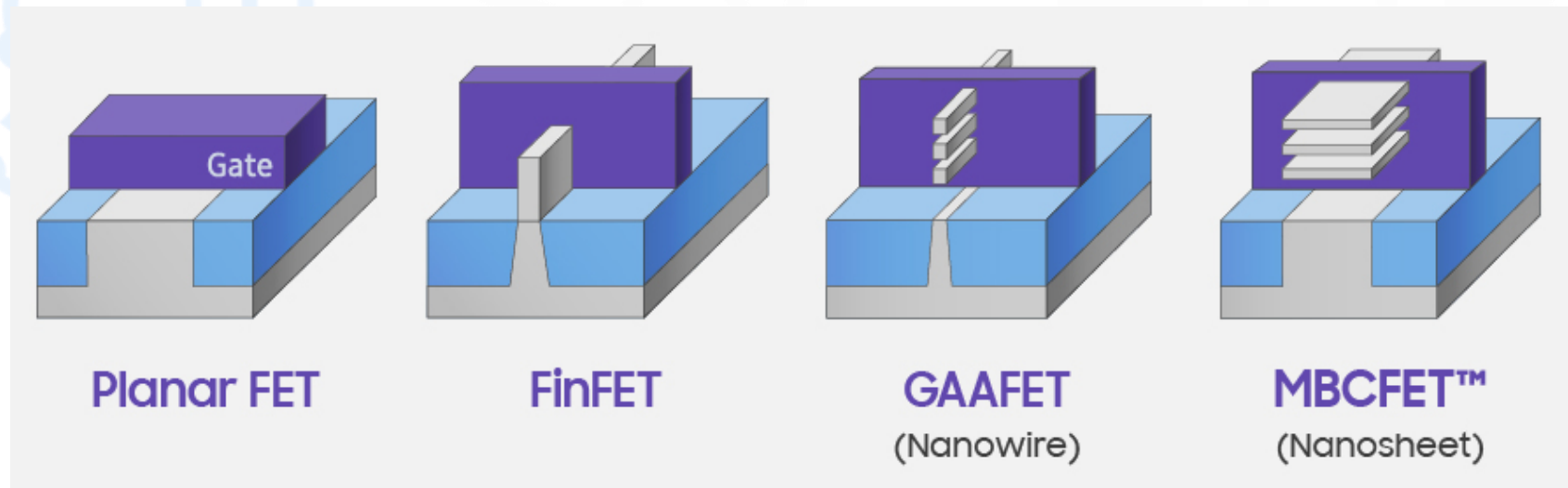
# Process Nodes

Planar	500 nm	FinFET	16 nm	FinFET Advantages
	350 nm		12 nm	
	250 nm		10 nm	
	180 nm		7nm	
	130 nm		5nm	
	90 nm		3nm	
	65 nm			
	45 nm			
	32 nm			
	28 nm			
	22 nm			

- Better control over the channel
- Suppressed short-channel effects
- Lower static leakage current
- Faster switching speed
- Low power consumption

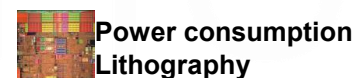
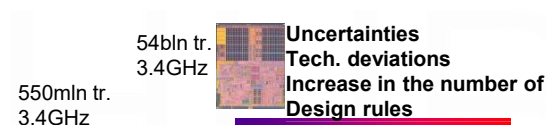
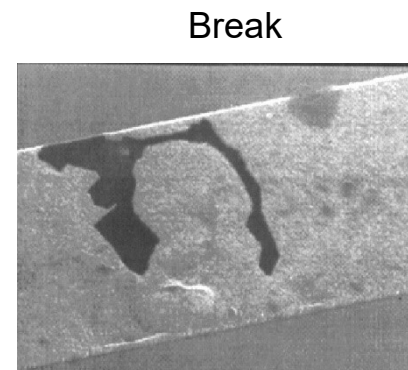
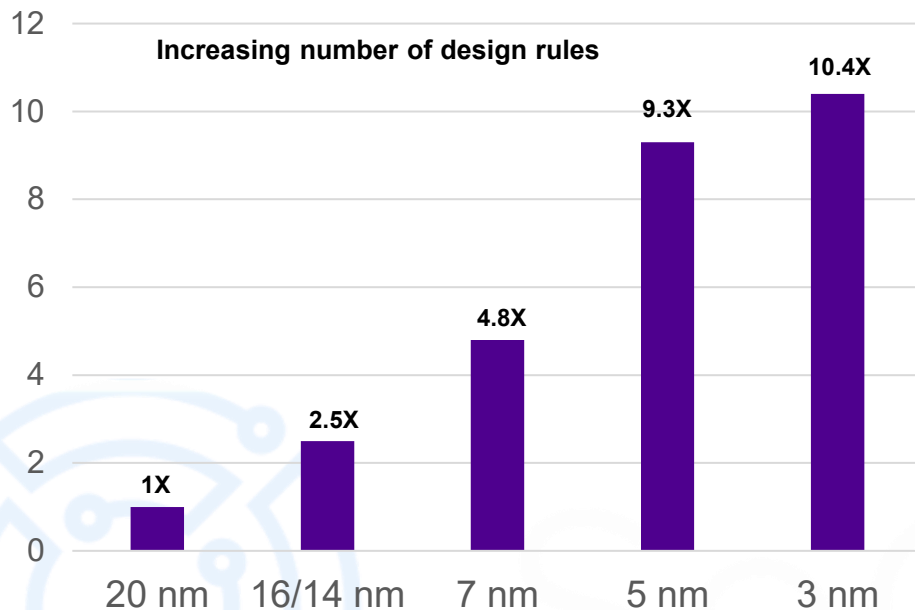
< 22 nm

< 3 nm



From <https://www.anandtech.com/show/16041/where-are-my-gaafets-tsmc-to-stay-with-finfet-for-3nm>

# IC Design Challenges



250mln tr.  
2.2GHz



**Signal Integrity**

42mln tr  
1.4GHz



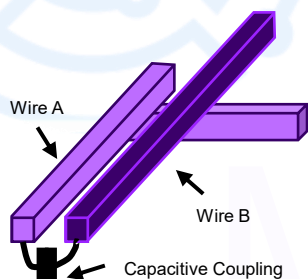
**Performance  
Interlayer connections**

7.5 Million Transistors.

7.5mln tr.  
300MHz



**Performance, area**

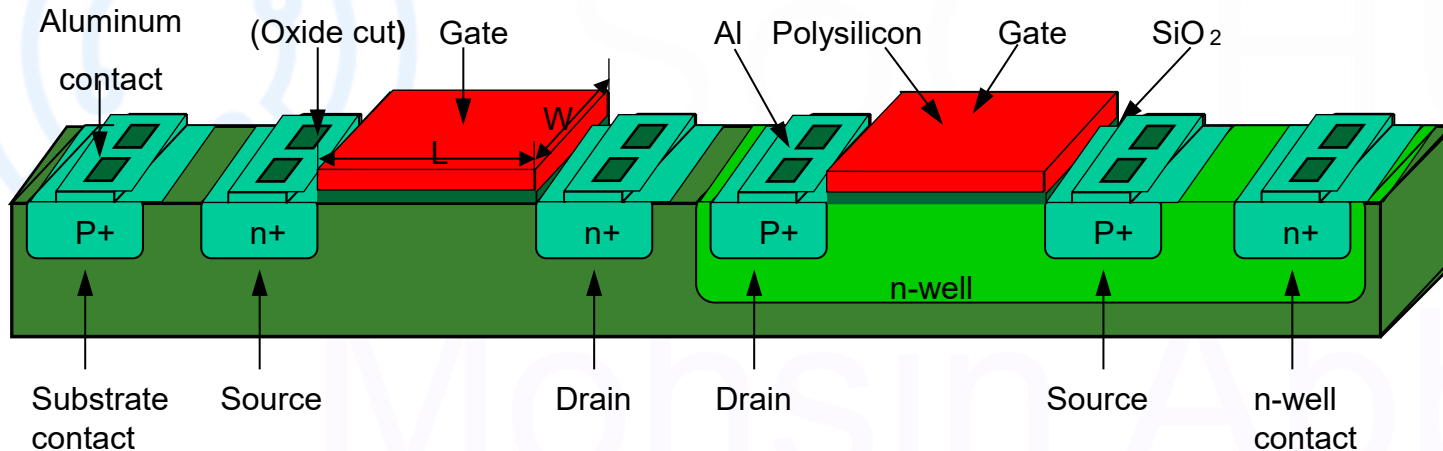
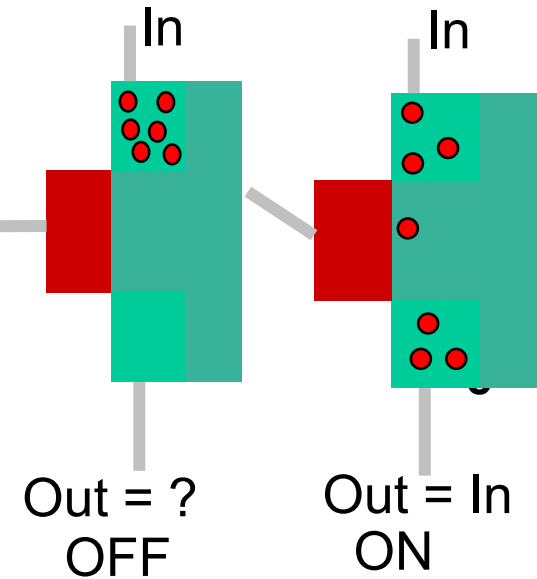
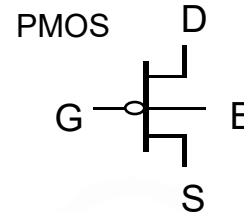
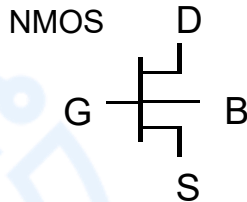
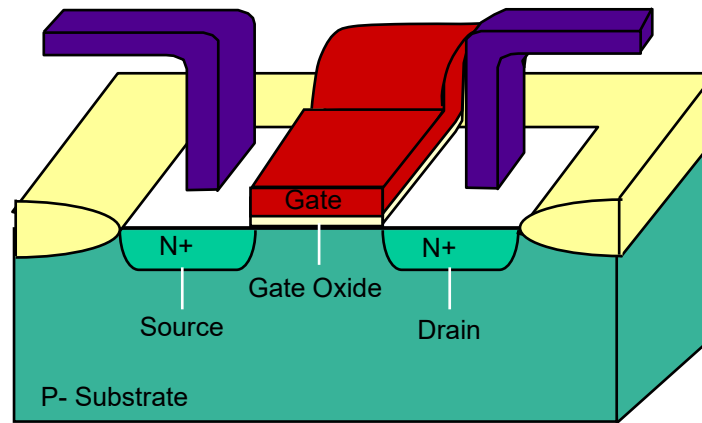


**Signal integrity**

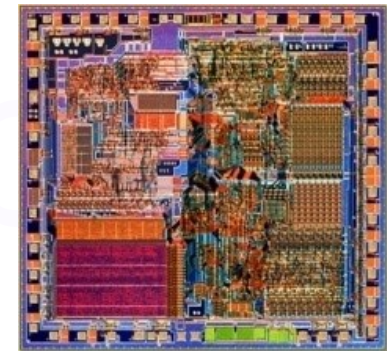
20um, 10um, 5um, 2um, 1um, 0.5um, 0.25um, 0.18um, 0.13um, 90nm, 65nm, 45nm, 32nm, 28nm, 22nm, 20nm, 14nm, 7nm, 5nm, 3nm

# Basic Element of IC

CMOS/MOS Transistor is a switch



For contemporary technologies, up to a dozen of billions switches on a single chip



# IC Components

## Digital Standard Cells

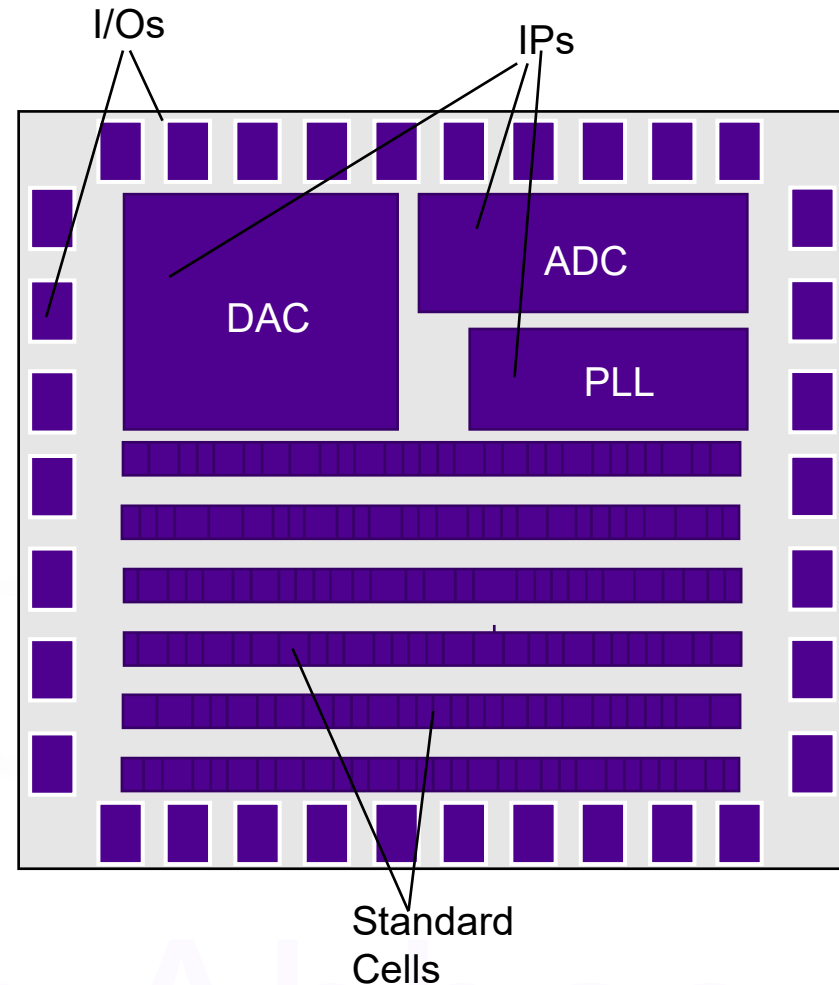
Basic cells performing simplest functions (e.g. AND, OR, etc.) or more complex functions (Multiplexers, Latches, Flip-Flops, etc.) used as building blocks for large digital circuits

## Input/Output (I/O) Cells

Implement the connection between IC inner circuitry and external environment (PCB)

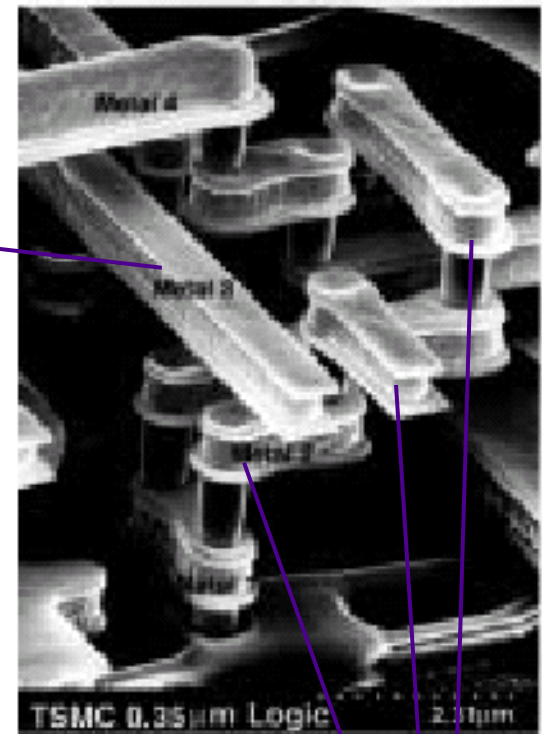
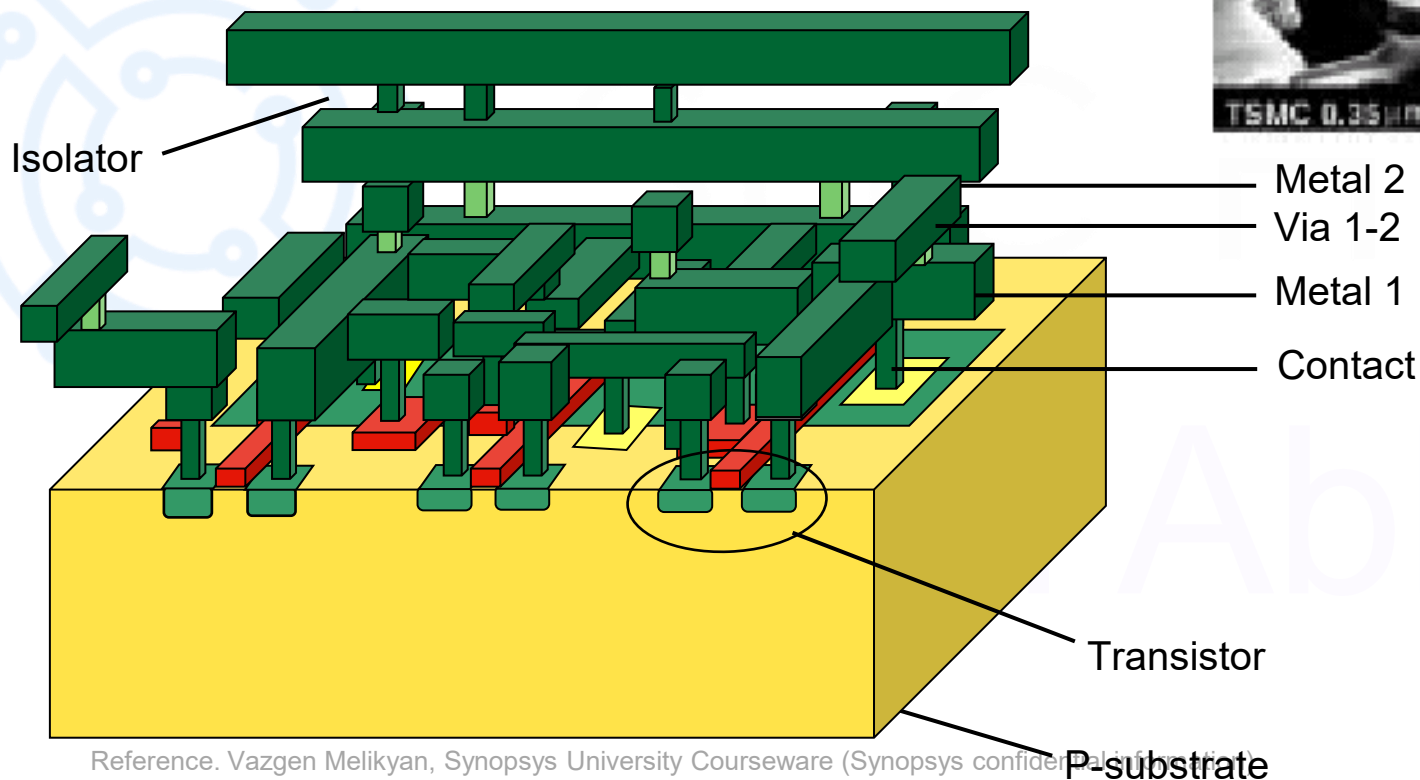
## Intellectual Property (IP) Blocks

Large blocks performing completed functions (DAC, ADC, PLL, etc), used in large designs





# IC as a Multi Layer Structure

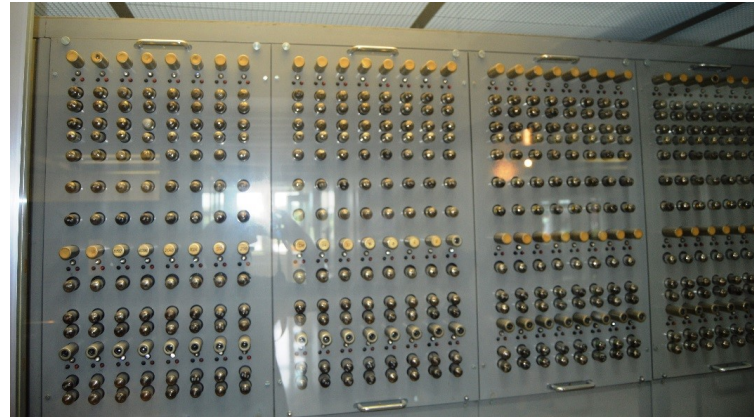


# History and Evolution of The IC Industry



## Vacuum tube

**1946.** The first electronic computers were created which operated by vacuum lamps

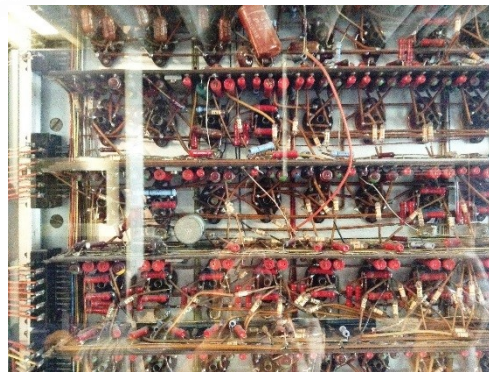


The first electronic “ENIAC” computer

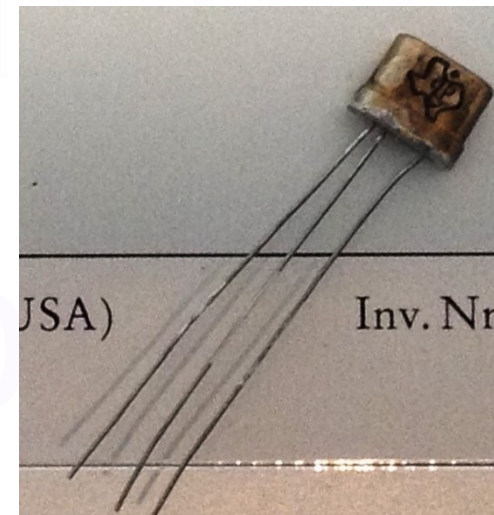


# History and Evolution of The IC Industry (Transistor Computers)

- 1948. The first transistor was created in Bell Labs
- 1954. The first fully transistor computer was developed.

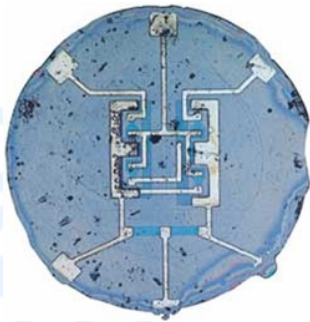


A block of fully transistor computer

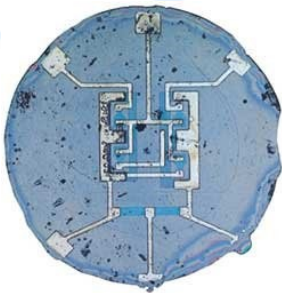


# The “Birth” of an IC

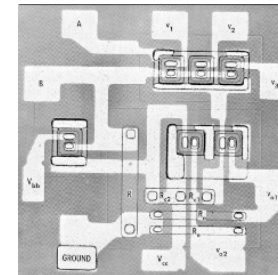
1959. The first integrated circuit was created



The first commercial IC which in 1959 was developed by the British architecture Robert Noyce and manufactured by “Texas Instruments”



1958: Robert Noyce



3-input Gate, which in 1966 was manufactured by Motorola

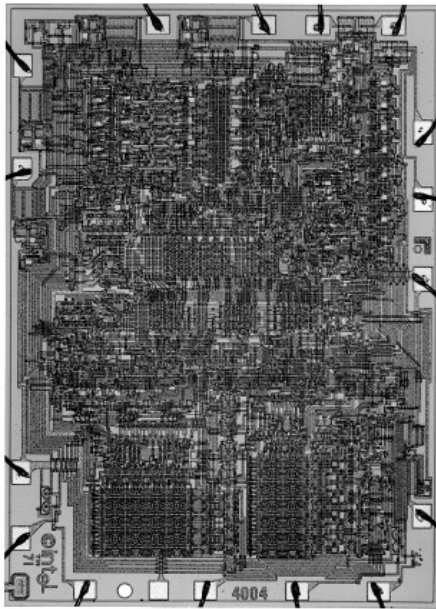


1959: Jack Kilby



# IC Based Computers

1971. The first microprocessor was created



Intel 4004 Microprocessor

- Developed in 1971
- Contained 1000 transistors
- 1 MHz operation

1983. Apple created the first PC





# Evolution of Integrated Circuits

## First integrated circuits

1958: Robert Noyce



1959: Jack Kilby



Only 66 years



## ● Today's integrated circuits



Google TPUv6



Qualcomm Snapdragon Gen 3

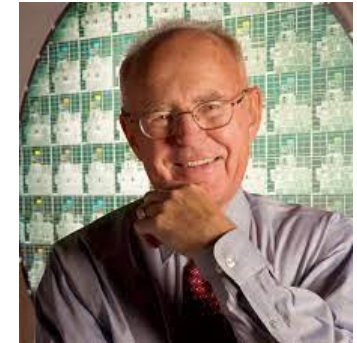
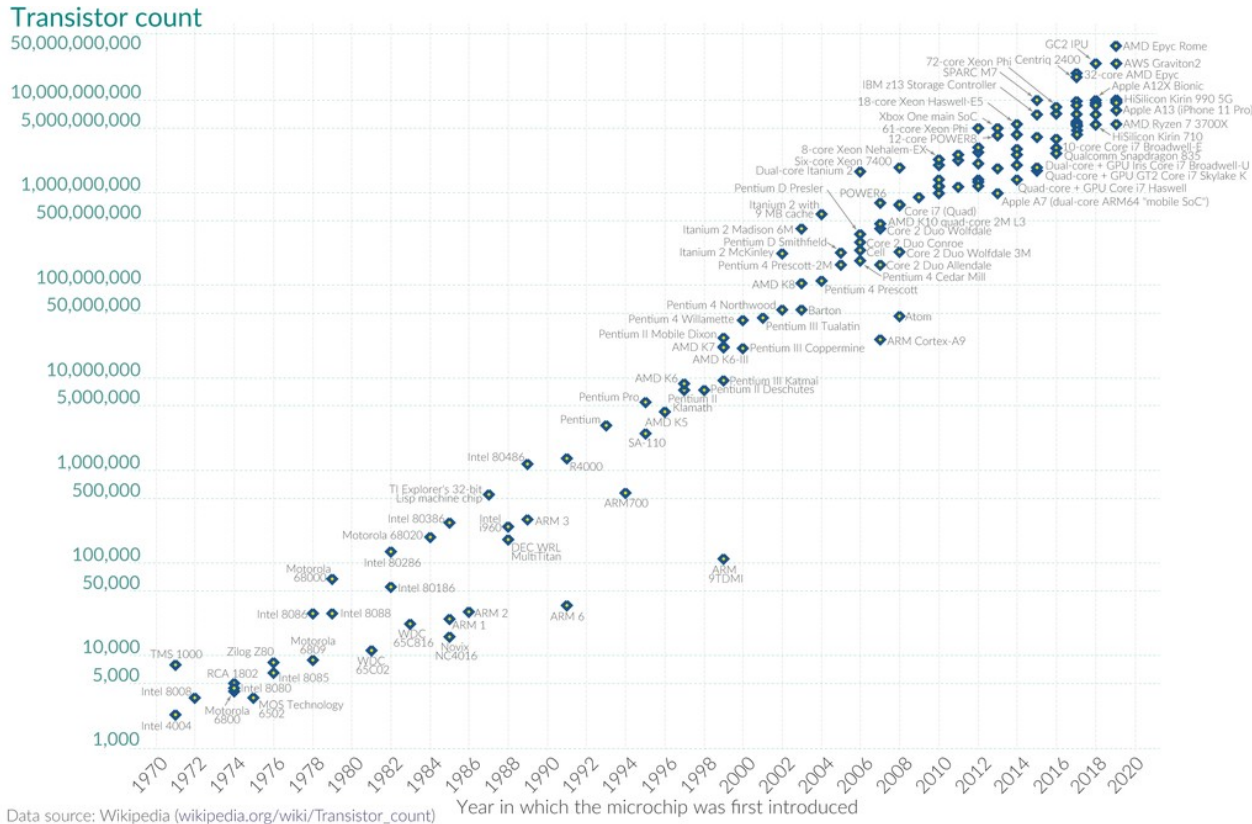


Huawei Kirin 9000e

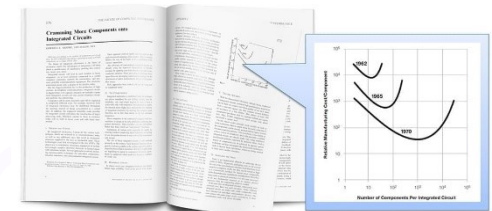


ARM Cortex-X5

# Moore's Law

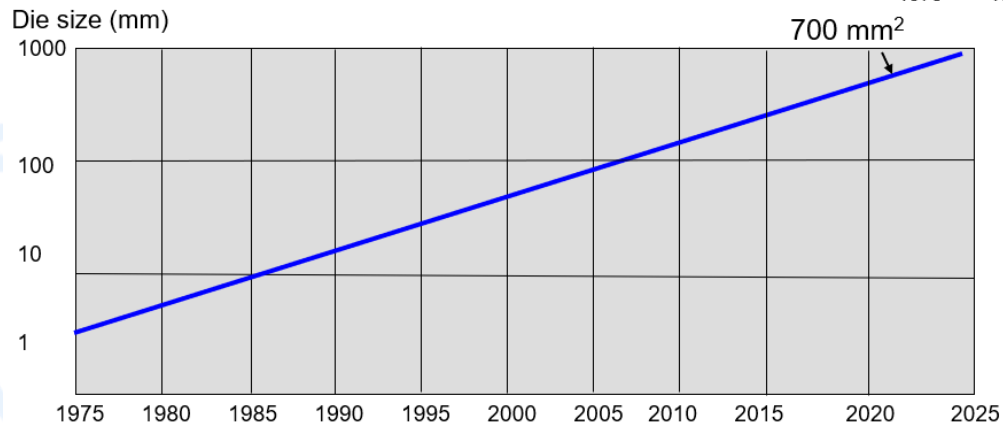
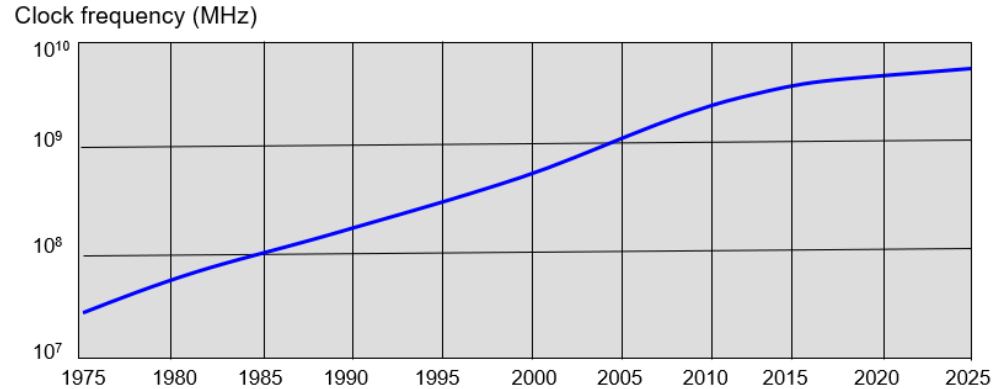


1965. The number of transistors in ICs will double every 18 months



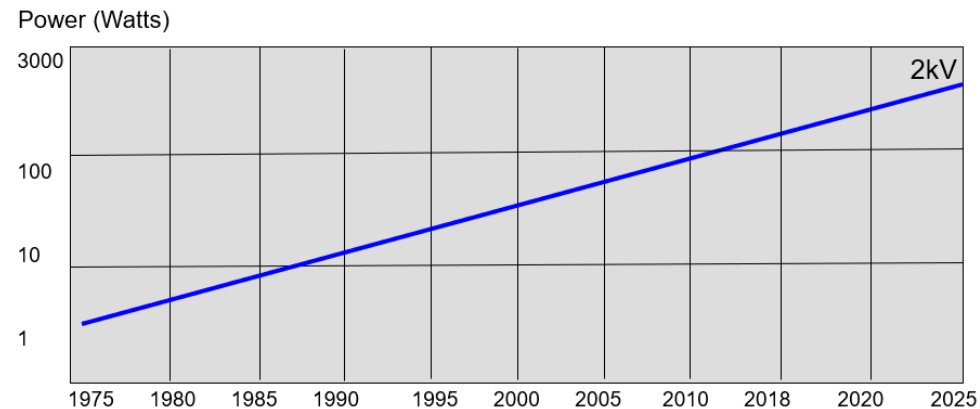
# History and Evolution of ICs

Clock frequency doubles every 2 years

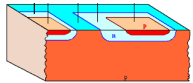


Die size grows by 14% every year

Powers increase about ten times every 3 years

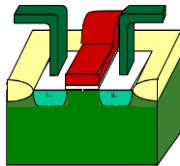


# IC Scaling



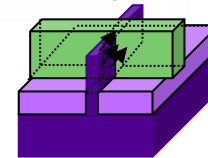
**Bipolar**

Less power consuming



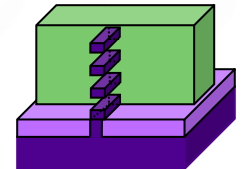
**MOS**

Less leakage current



**FinFET**

Less leakage current



**GAA**

20um

...

2um

...

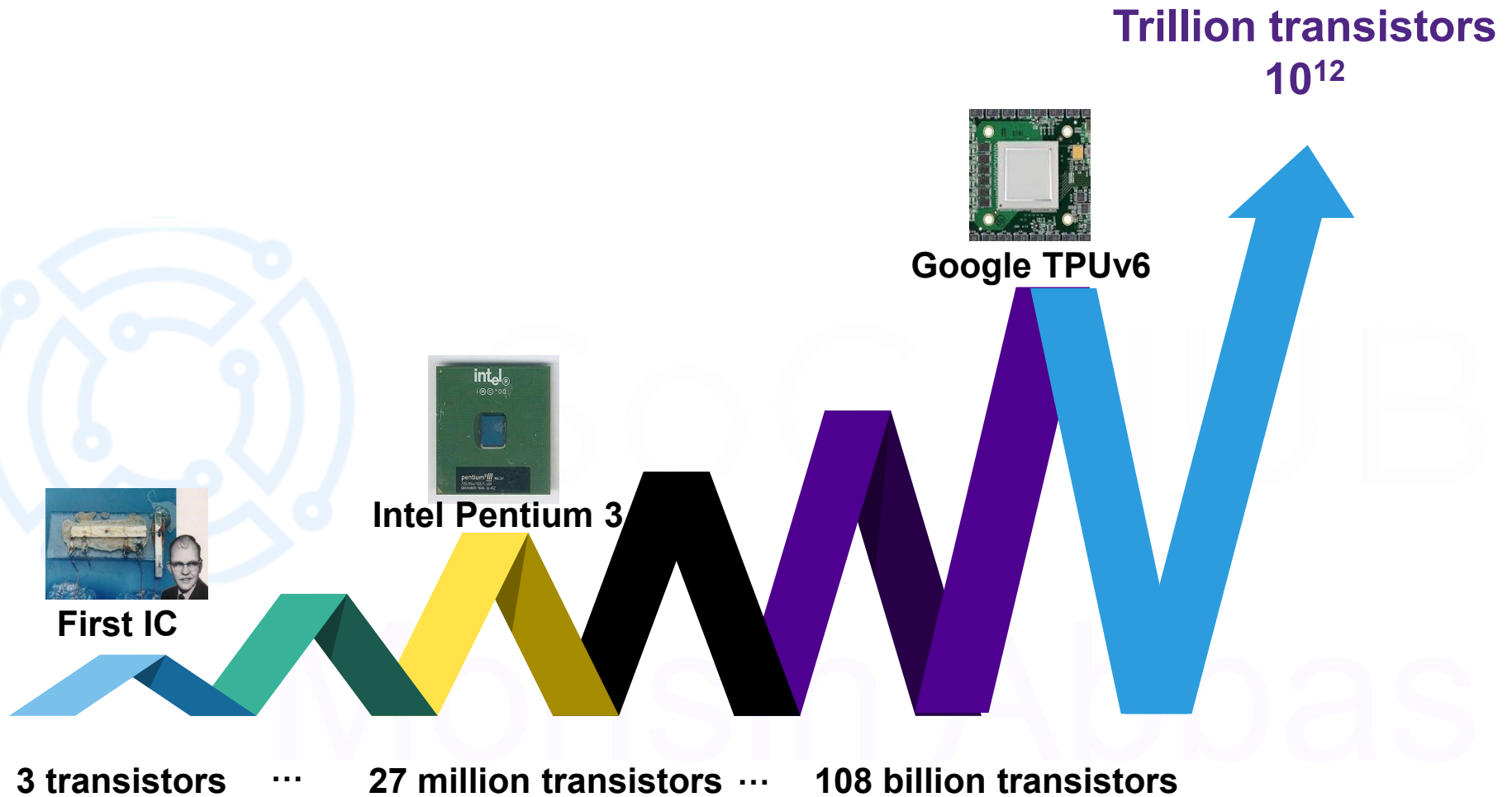
14nm

...

2nm

- Reduction of transistor size ~10000 times
- Change of transistor type 4 times

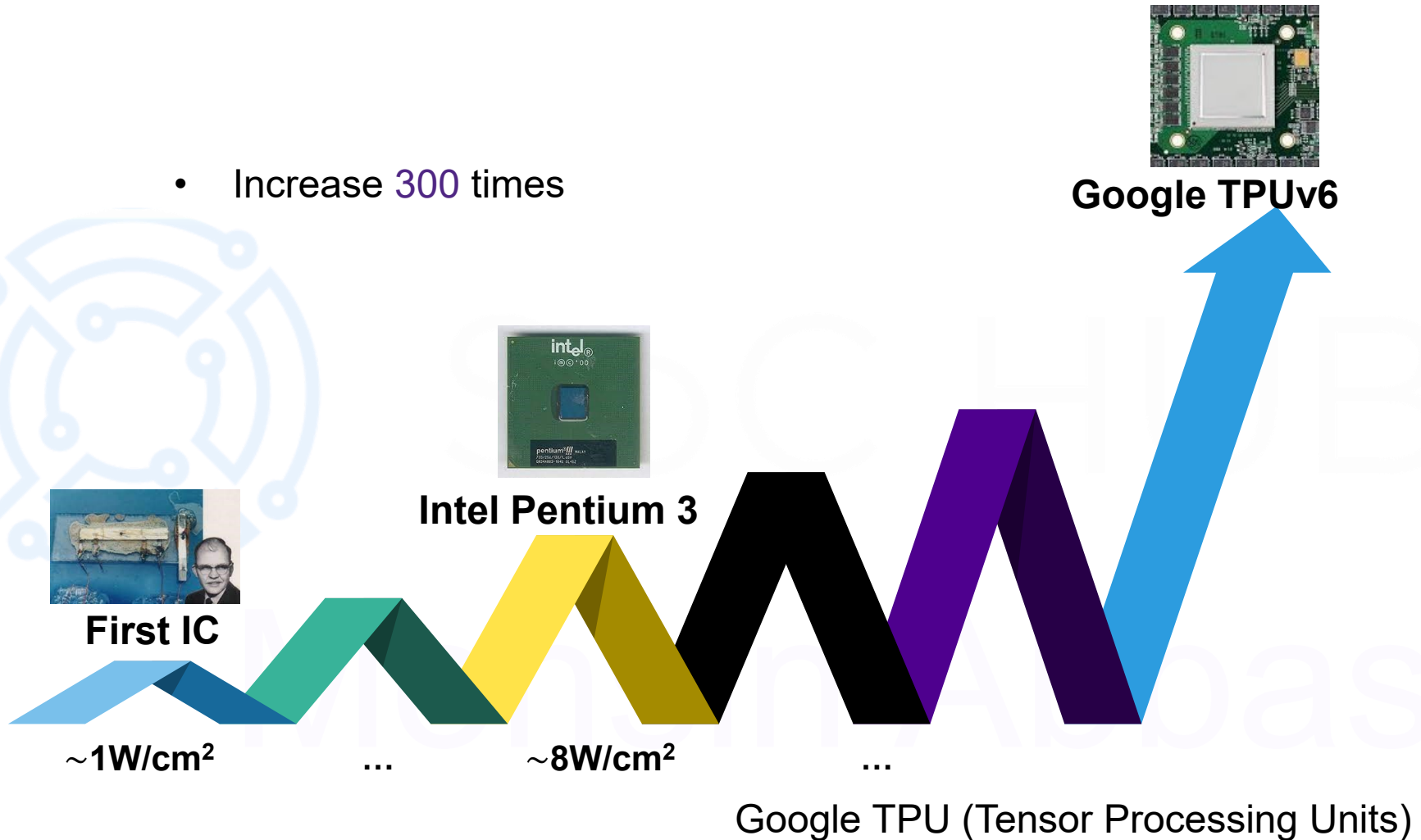
# IC Scaling



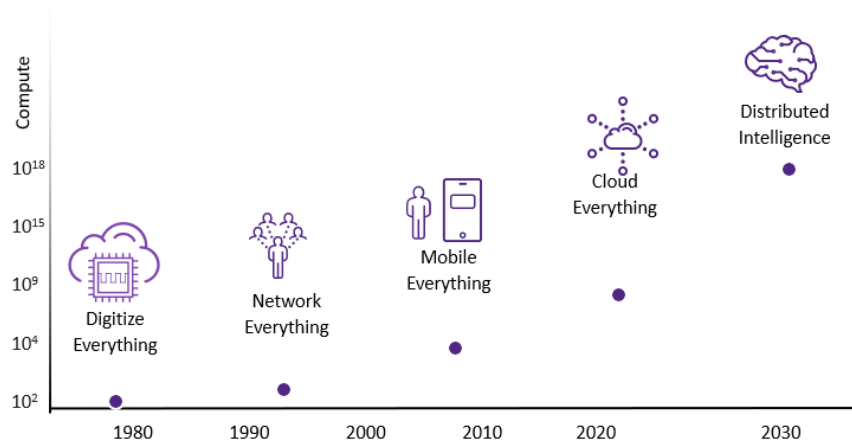


# Increase of Specific Power Consumption

- Increase 300 times



# Era of Innovations



100B

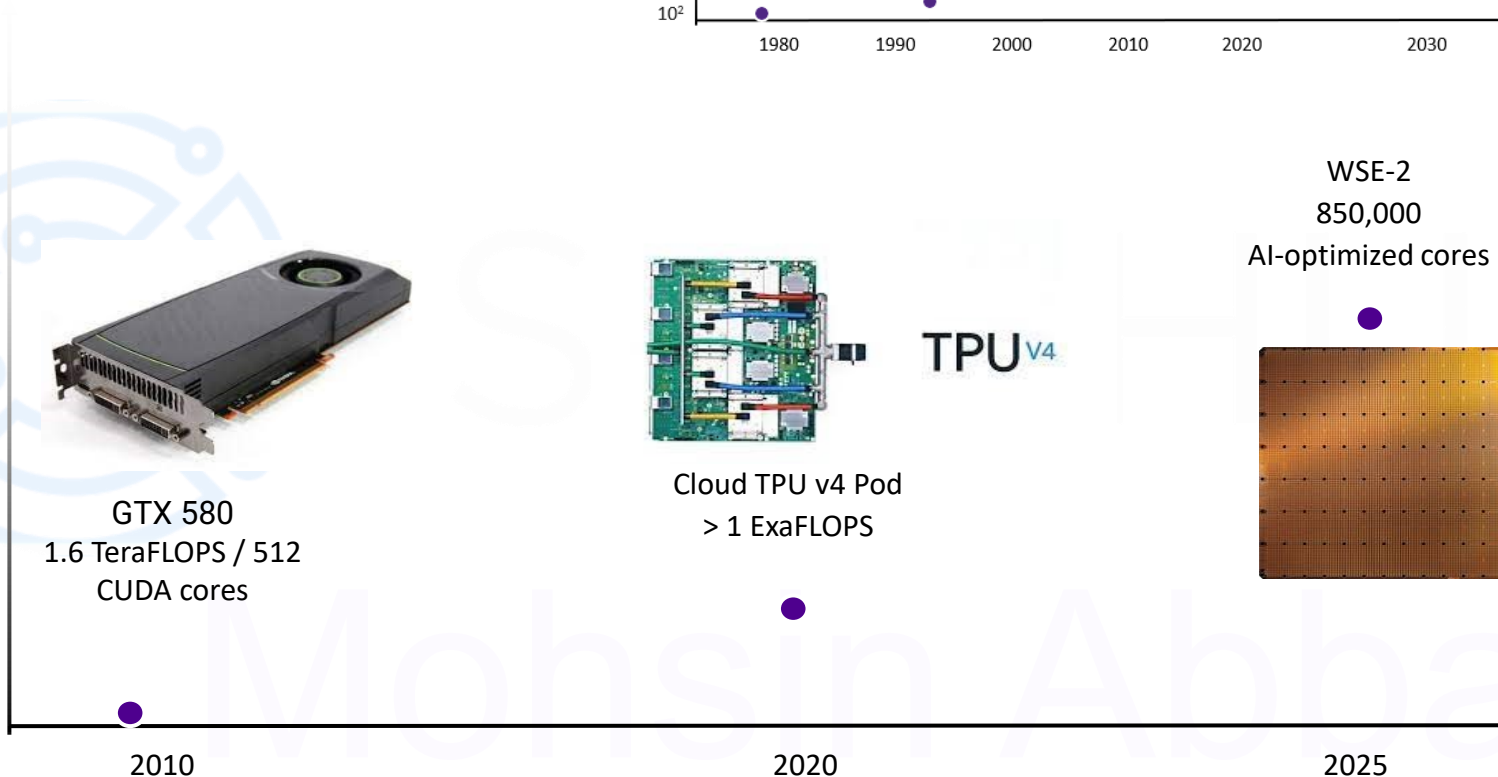
Intelligent  
Connected  
Devices

World to generate

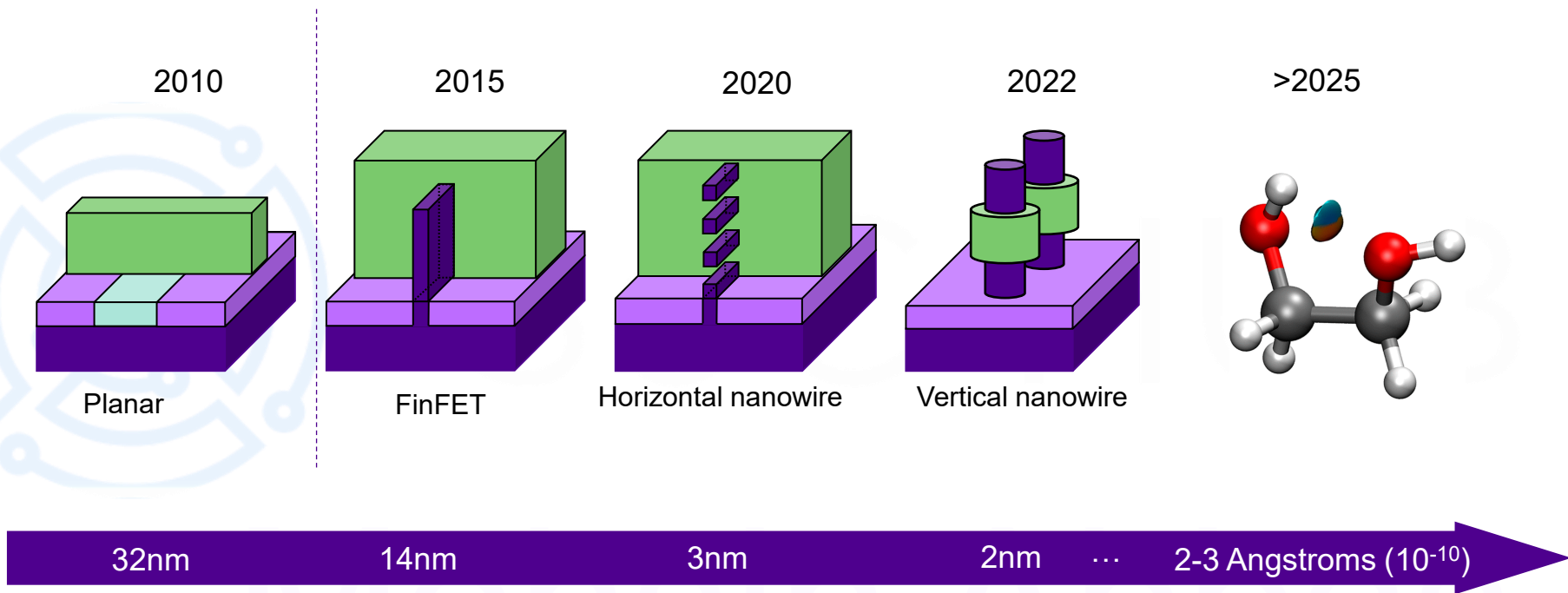
175

Zettabytes  
of data by 2025

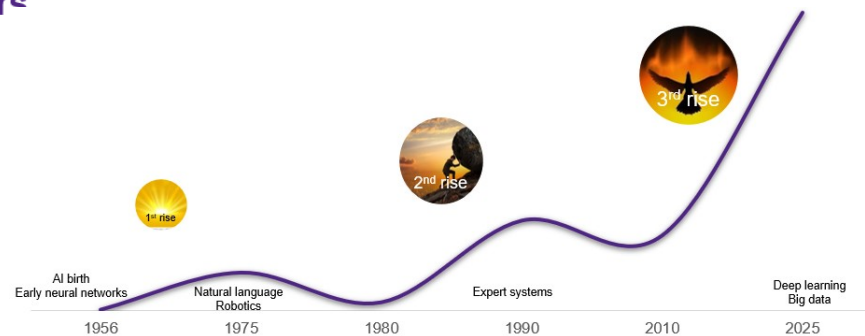
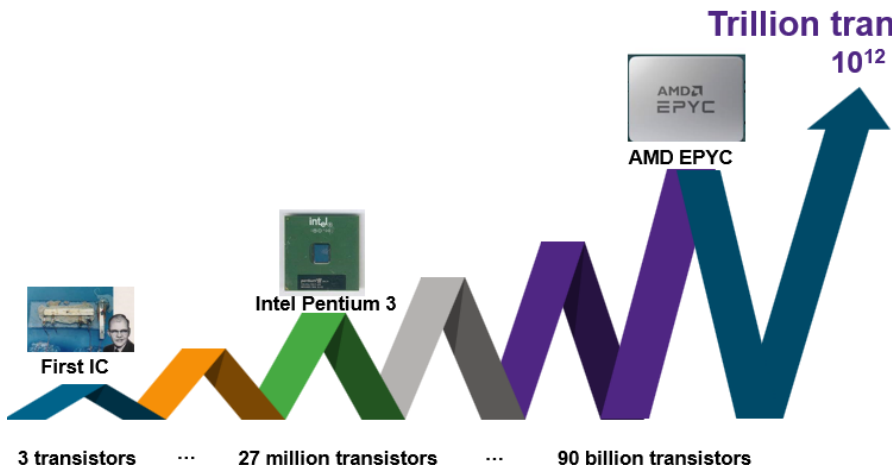
Computing power



# New Era: Further Scaling

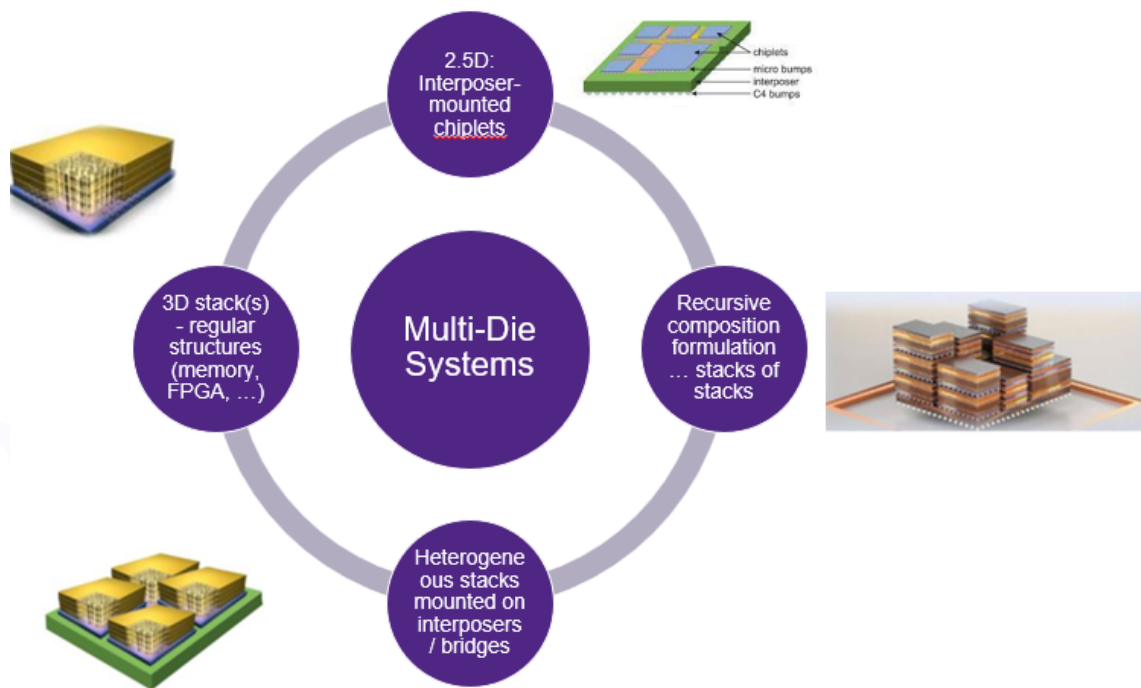


# New Era: Further Scaling



Intensive Use of AI

Transition from Monolithic to Multi-Die Systems



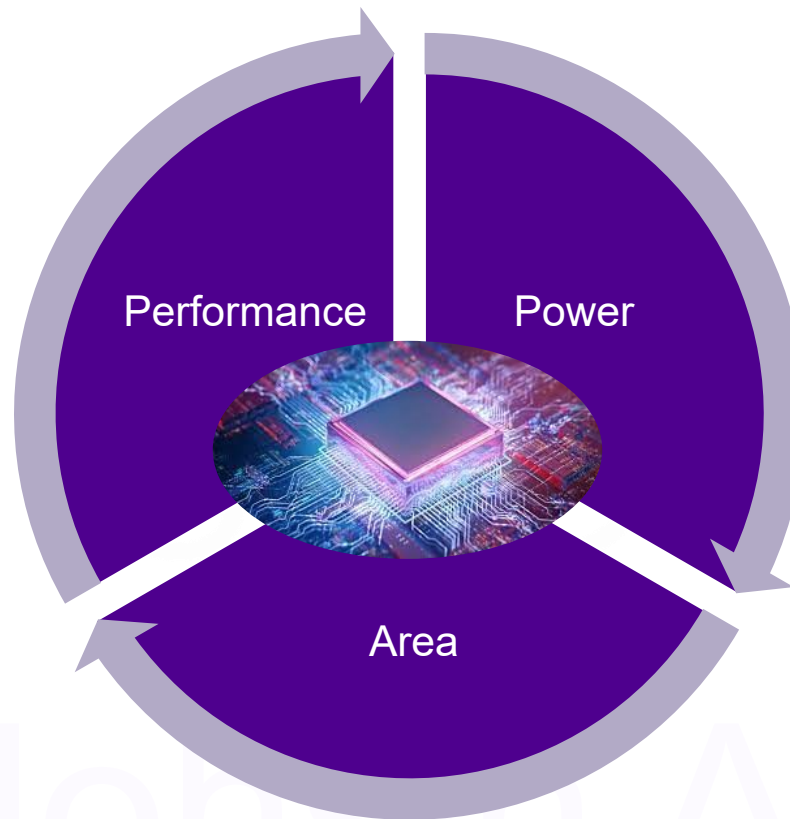
# Semiconductor Industry Association (SIA) Roadmap

Date	1999	2005	2010	2018	2025
Technology (nm)	180	65	28	5	1
Minimum mask count	24	25	27	30	50
Wafer diameter (mm)	200	400	400	450	500
Memory samples (bits)	1G	8G	32G	10T	100T
Transistors/cm <sup>2</sup>	6.2M	180M	330M	1.5G	20 G
Maximum number of metal layers	6-7	9	9	12	25
Clock frequency (MHz)	1250	3200	5200	20000	35000
IC sizes (mm <sup>2</sup> )	400	596	699	750	1200
Power supply (V)	1.5-1.6	0.8-1.2	1.2-1	0.37-0.42	0.28-0.33
Number of pins	700	1957	2734	3350	4200
Number of pins	700	1957	2734	3350	4200

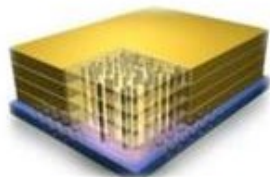
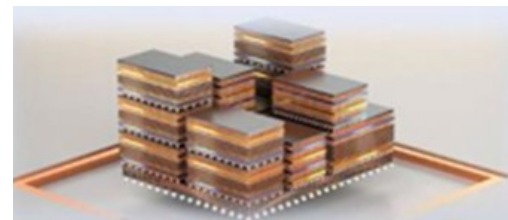
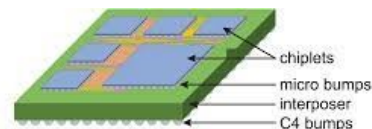
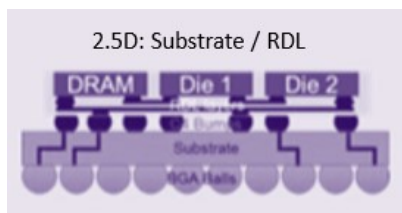




# IC Design – PPA Analysis



# Multi-Die Systems: Types



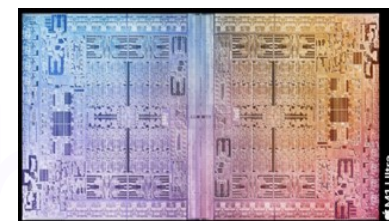
3D stack(s) -  
regular  
structures  
(memory,  
FPGA, ...)

Multi-  
Die  
Systems

Recursive  
composition  
formulation ...  
stacks of  
stacks

Heterogeneous  
stacks mounted  
on interposers /  
bridges

APPLE - M1  
UltraMax CPU



2x Dies, 114B  
Transistors

# IC Design Steps



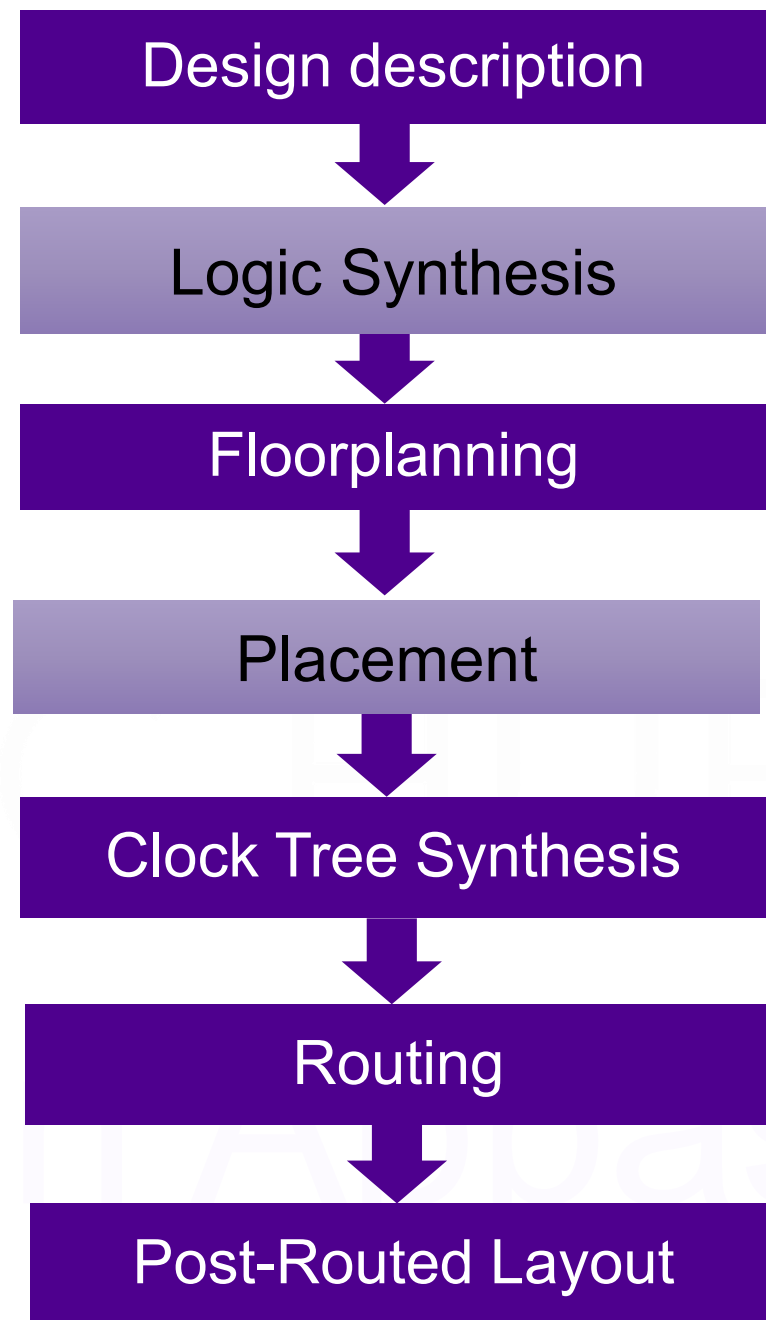
GDSII is binary format (Not Readable)

- You can try though ....

## Inverter.gds

```

02000200 60000201 1C000300 02000600 .....`.... 000000
01000E00 02000200 60002500 01000E00 .....%.`..... 000010
42494C45 4C504D41 58450602 12002500 .%....EXAMPLELIB
000020
413E0503 14000300 02220600 59524152 RARY..".....>A
000030
1C00545A 9BA02FB8 4439EFA7 C64B3789 .7K...9D./..ZT..
00004
60000000 01000E00 02000200 60000205 ...`.....` 000050
58450606 0C001100 01000E00 02000200 .....EX 000060
0100020D 06000008 04000045 4C504D41 AMPLE.....
000070
  
```





# IC Design Steps: Logic Synthesis


## HDL (Verilog)

### ■ General definition

```
module module_name ( port_list );  
    port declarations;  
    ...  
    variable declaration;  
    ...  
    description of behavior  
endmodule
```

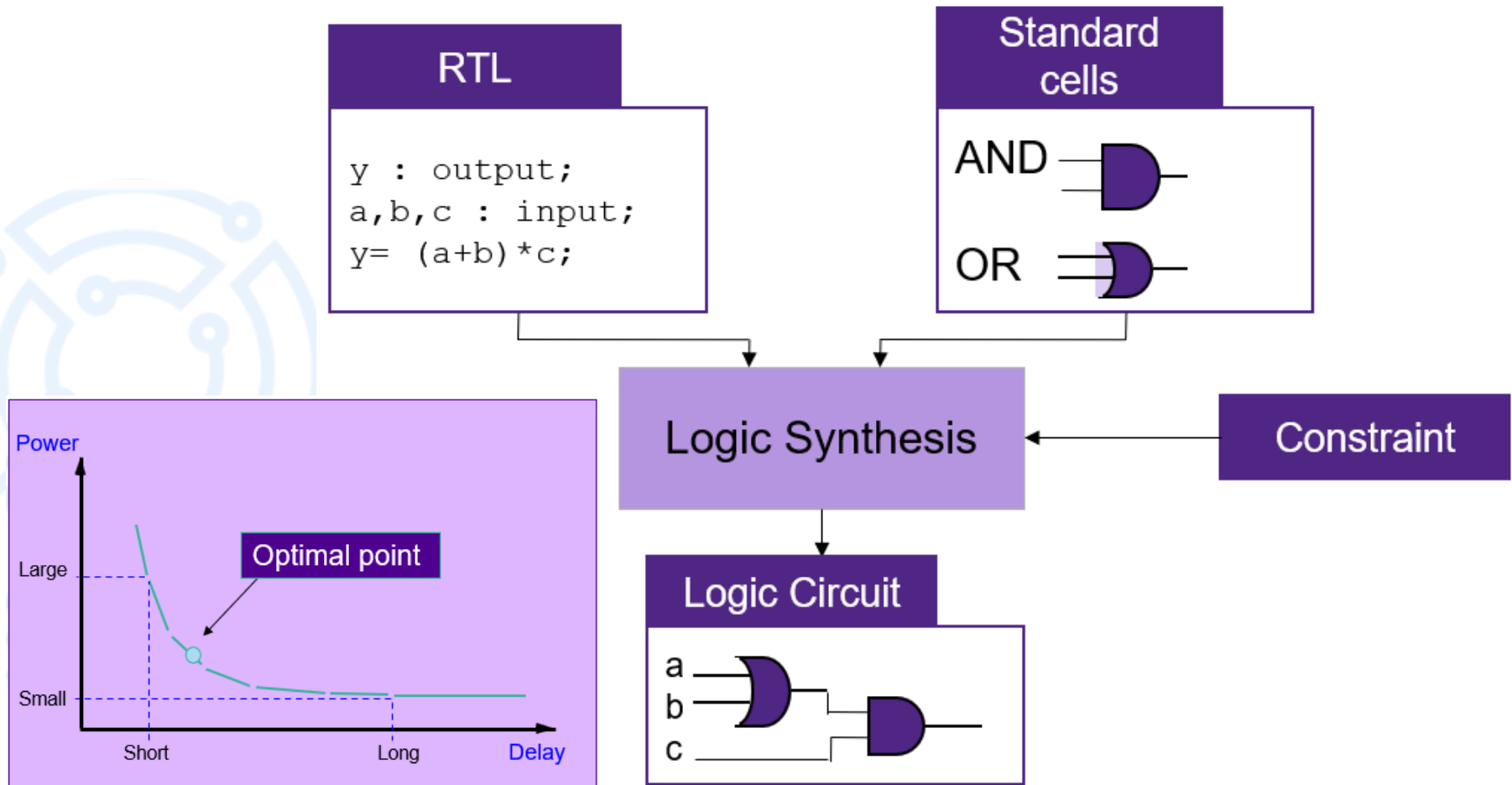
### ■ Example

```
module half_adder(a, b, sum, carry);  
    input a, b;  
    output sum, carry;  
  
    assign sum = a ^ b; // ^ denotes XOR  
    assign carry = a & b; // & denotes AND  
endmodule
```

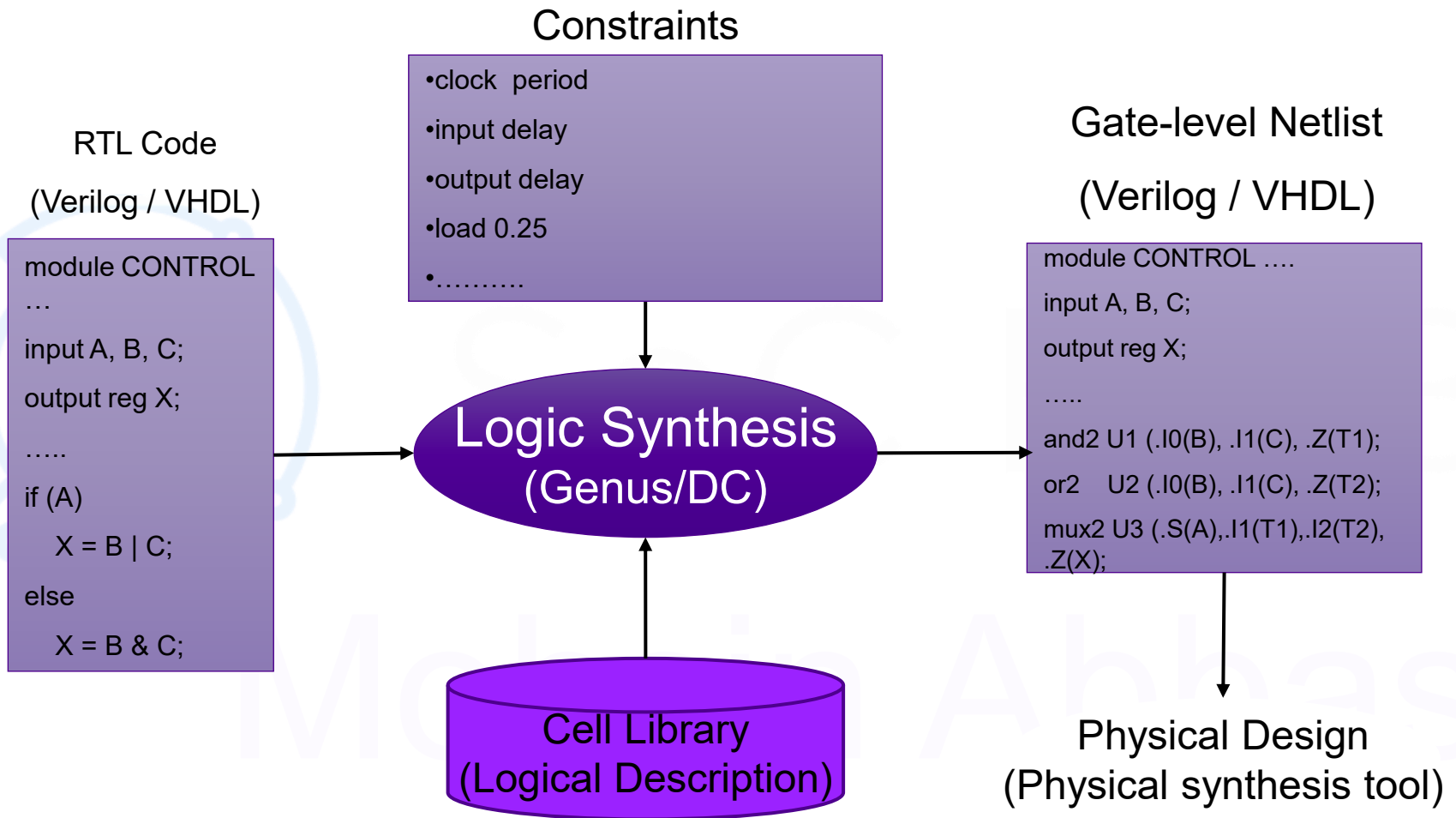




# IC Design Steps: Logic Synthesis



# IC Design Steps: Floorplanning

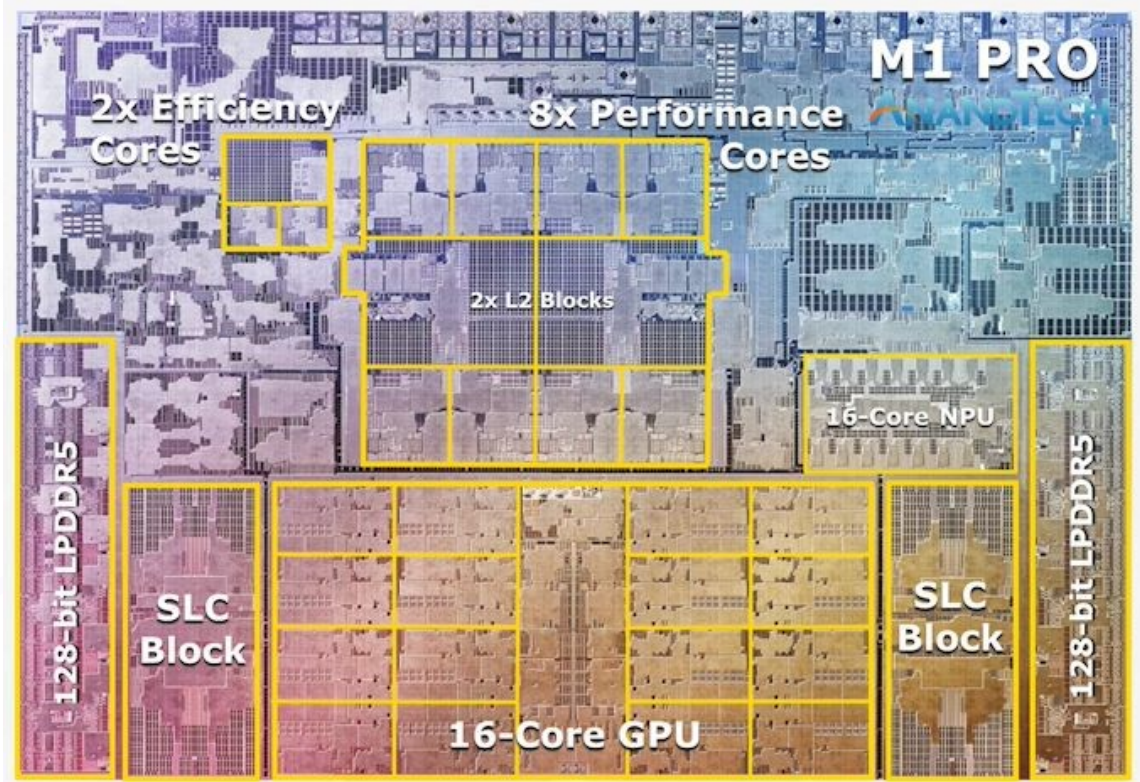


# IC Design Steps: Floorplanning

- Floorplanning is a critical phase in ASIC design, where the layout and organization of various components — such as I/O pads, macros, and power/ground structures — are defined on the chip.
  - It sets the stage for subsequent design steps, including placement, routing, and timing closure.

## Apple M1 : Floorplan

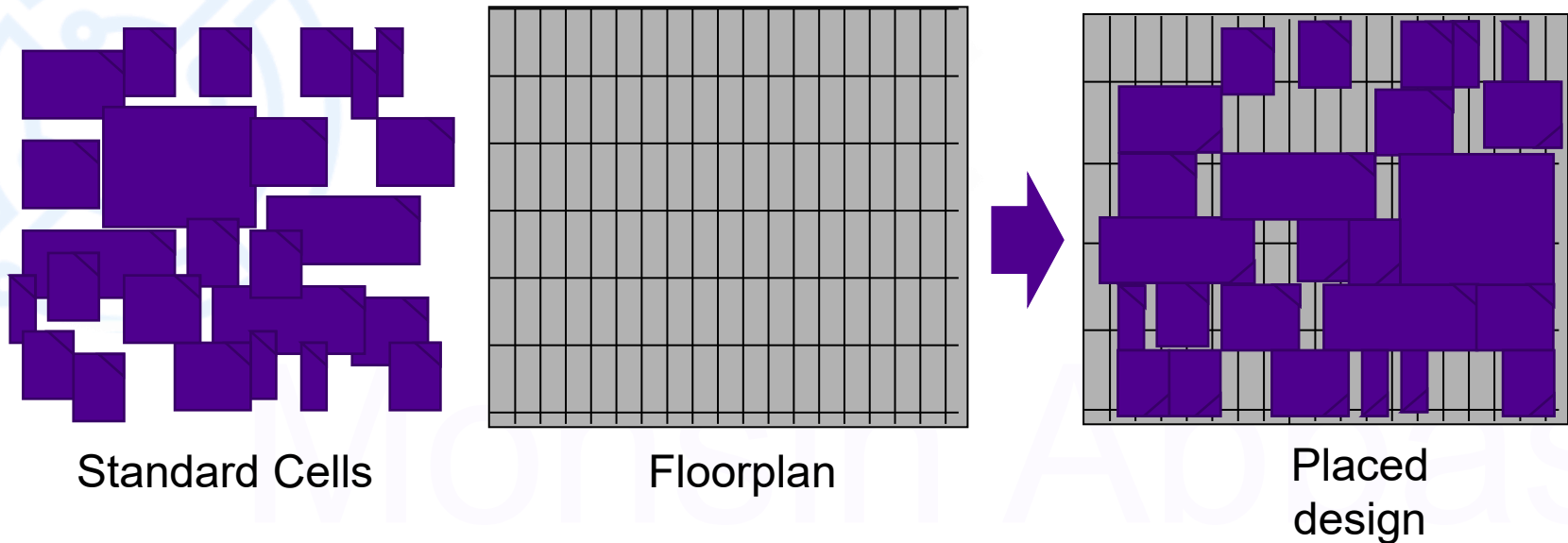
Basically a good floorplan will give a better Power Performance Area (PPA).



# IC Design Steps: Placement

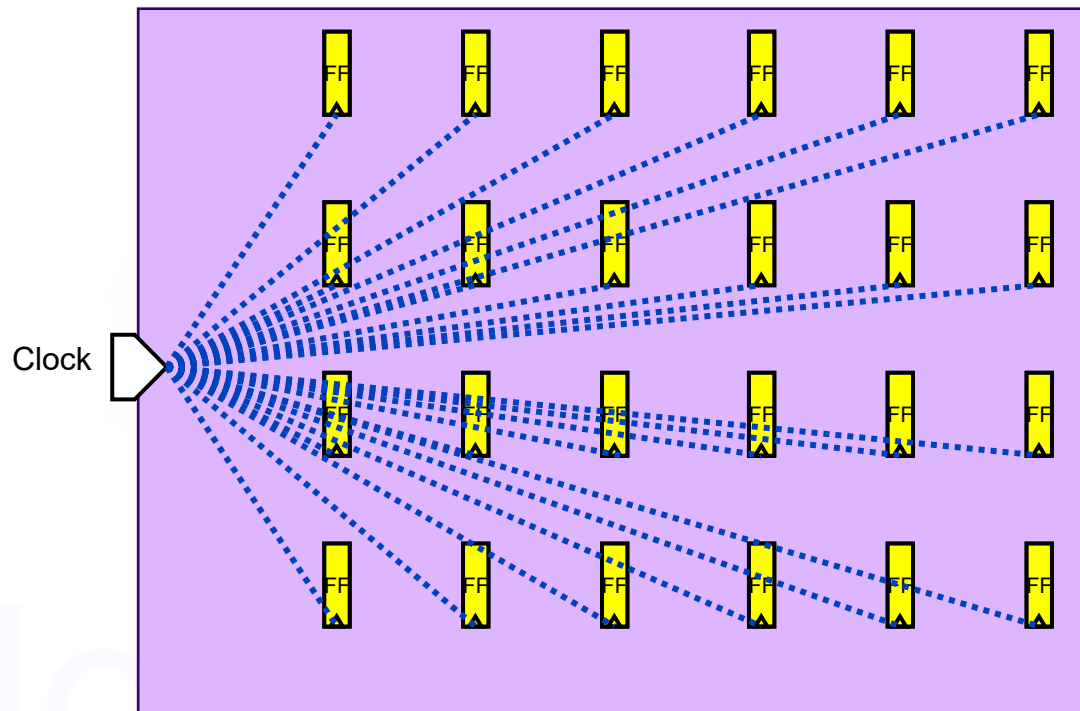
Placement is the stage where the Standard Cells are placed in the design.

- Previously in the floorplan stage **Macro** placement is done.
- Placement does not just place the standard cell available in the synthesized netlist, it also optimizes the design.



# IC Design Steps: Clock Tree Synthesis

- All clock pins are driven by a single clock source

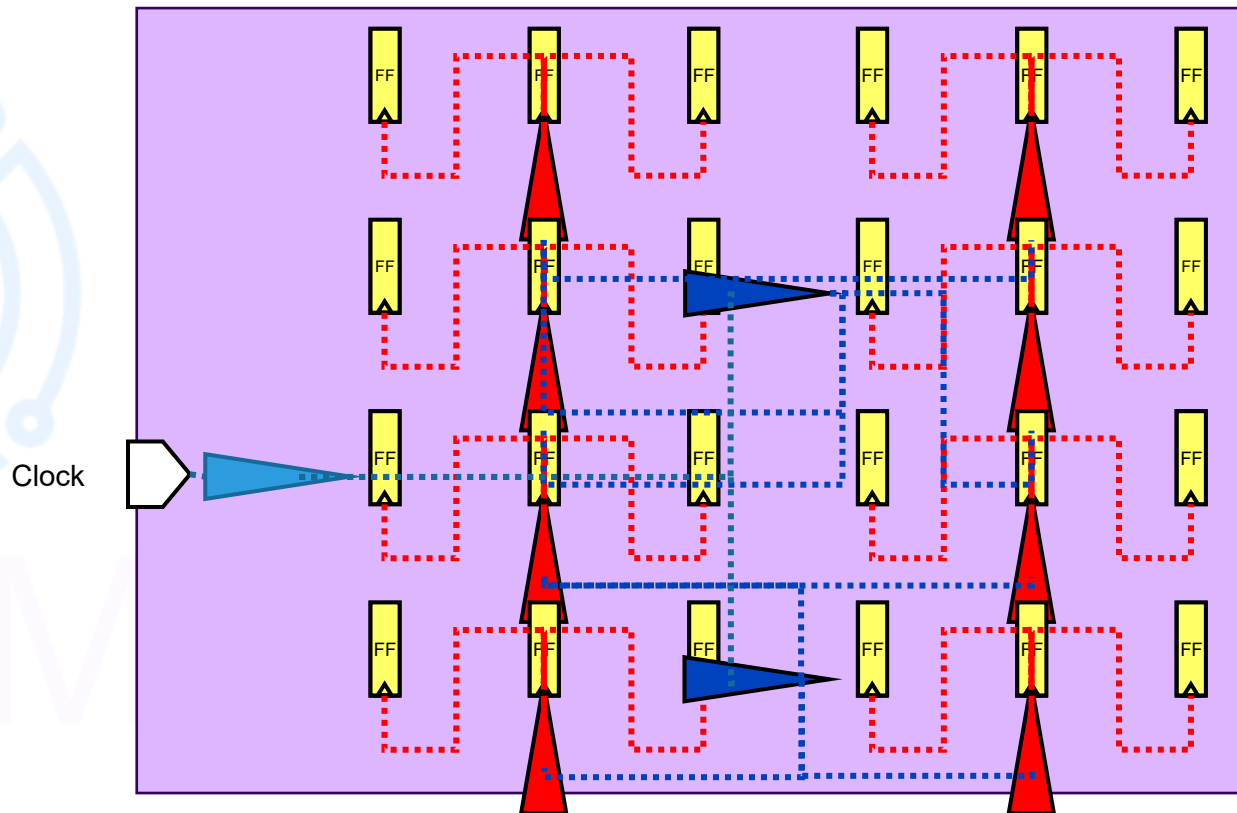


**Problems ?**



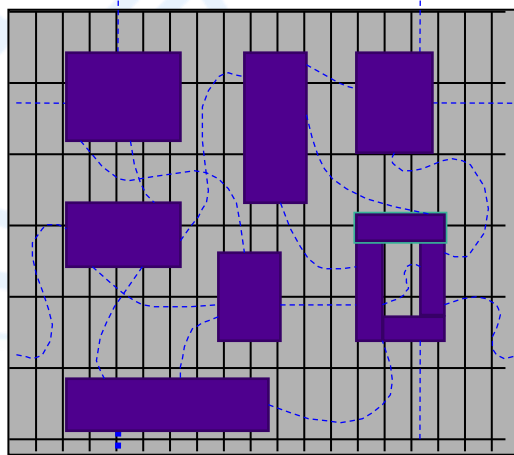
# IC Design Steps: Clock Tree Synthesis

- A buffer tree is built to balance the loads and minimize the delays

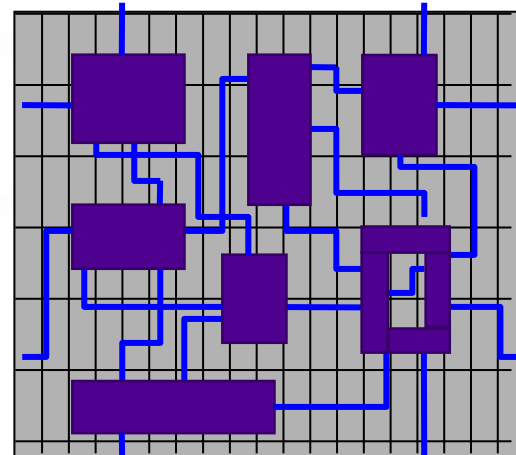


# IC Design Steps: Routing

- Routing is the stage after **Clock Tree Synthesis** and optimization
  - Exact paths for the interconnection of standard cells, Macros, clock and signal (I/O) pins are generated.
  - Electrical (physical) connections using metal interconnects ( and vias) are created in the layout



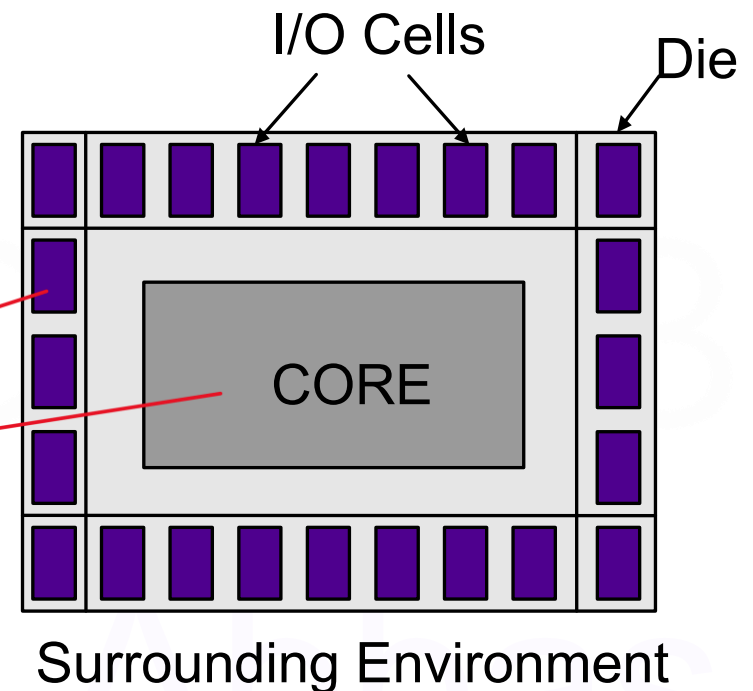
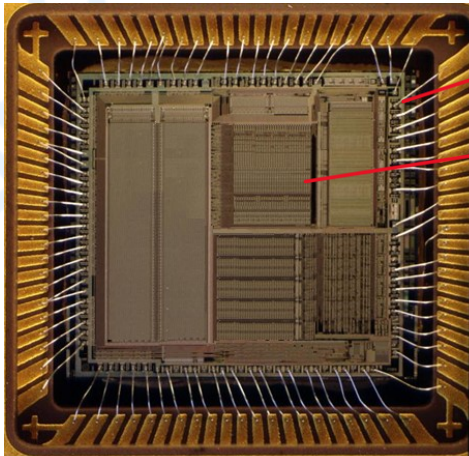
Placed design



Routed design

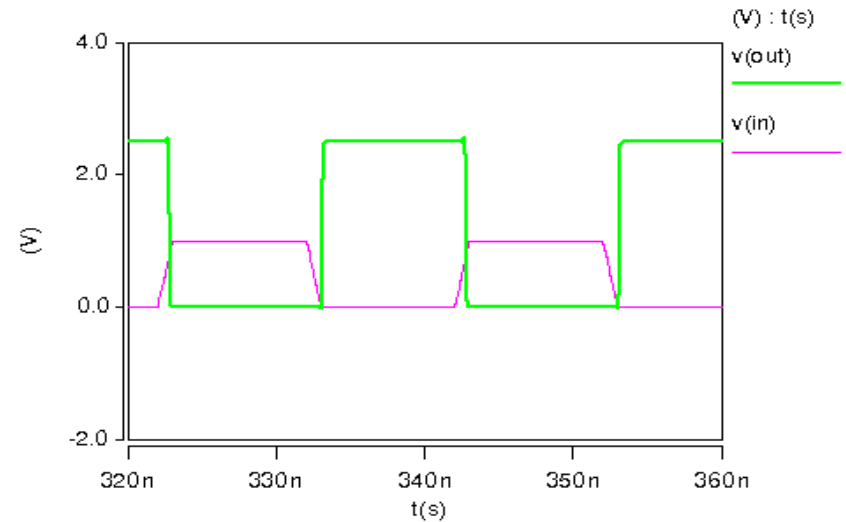
# IC Design Steps: I/O Design

- **Core** - provides basic functionality of IC
- **I/O Cell** – provides interface between the Core and surrounding environment (voltage levels, signal transfer velocity, resistances, etc.)



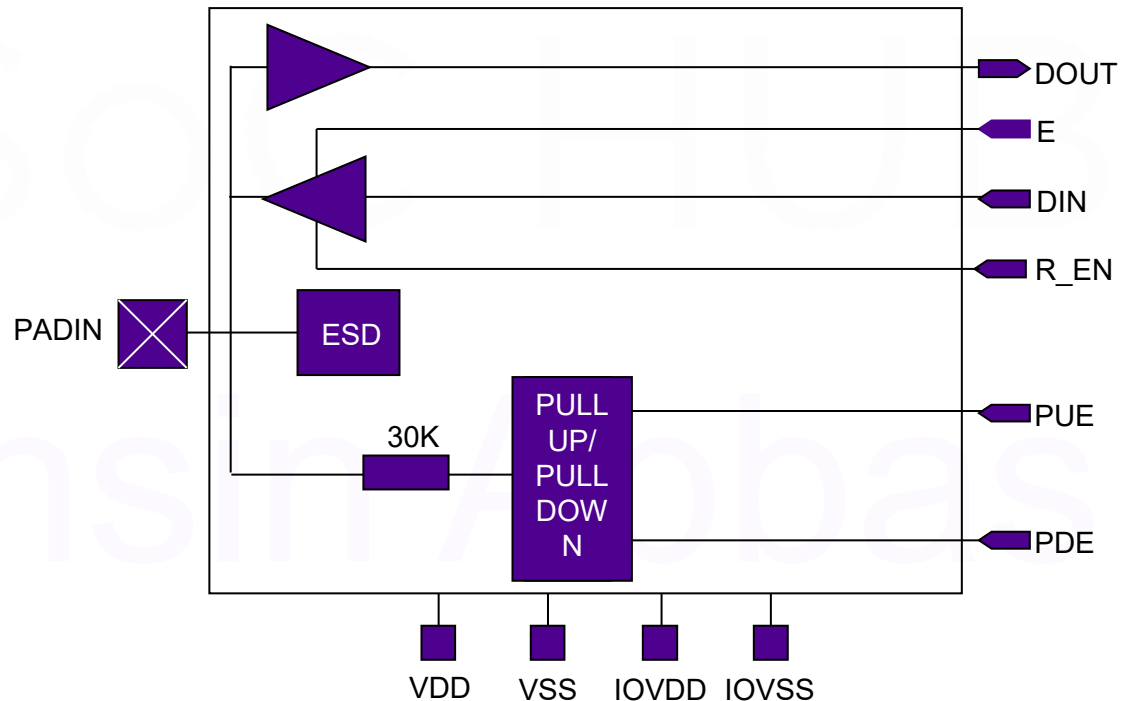
# IC Design Steps: I/O Design

## VDD=1.0V – to - VDDIO=2.5V



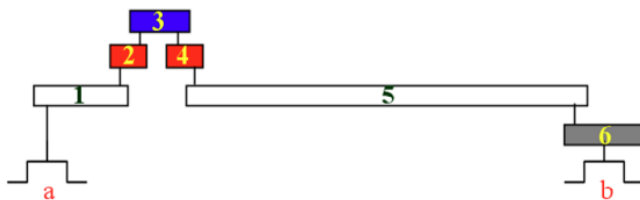
# ESD protection

- IC is very sensitive to electrostatic discharge, I/O cell should protect IC from ESD.
- IC is subject to ESD during fabrication, packaging and exploitation processes.

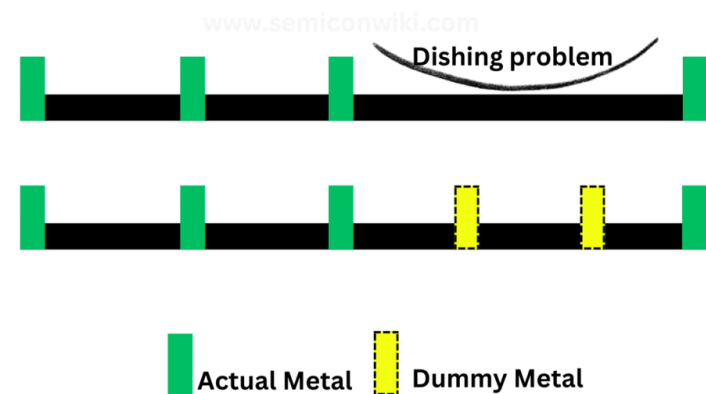
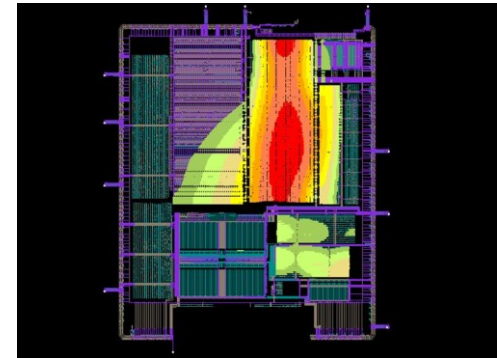
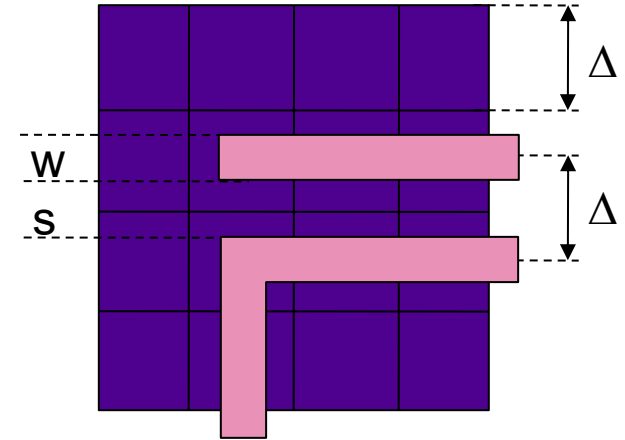


# IC Design Steps: Sign-Off

- Sign-Off is the process of logical and physical verification of the chip/IC.
  - Logical
    - Logic Equivalence Checks
    - Post-layout STA
  - Physical
    - Layout Vs Schematic (LVS)
    - Design Rule Checks (DRCs)
    - Electric Rule Checks (ERC)
    - Antenna Checks
  - Power
    - Electro-Migration (EM)
    - IR Drop



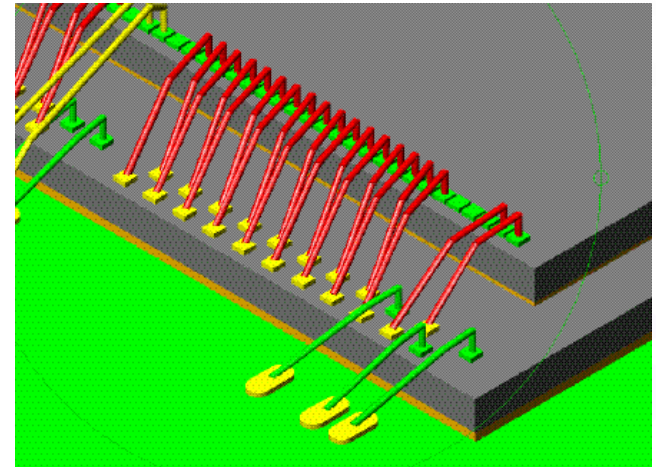
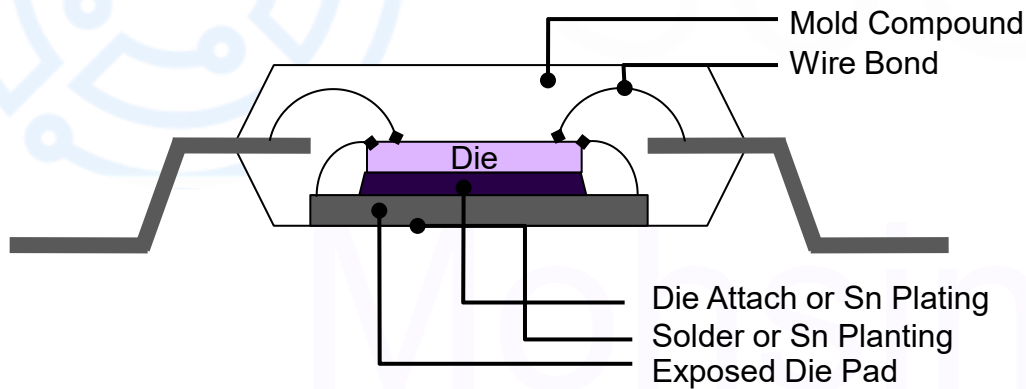
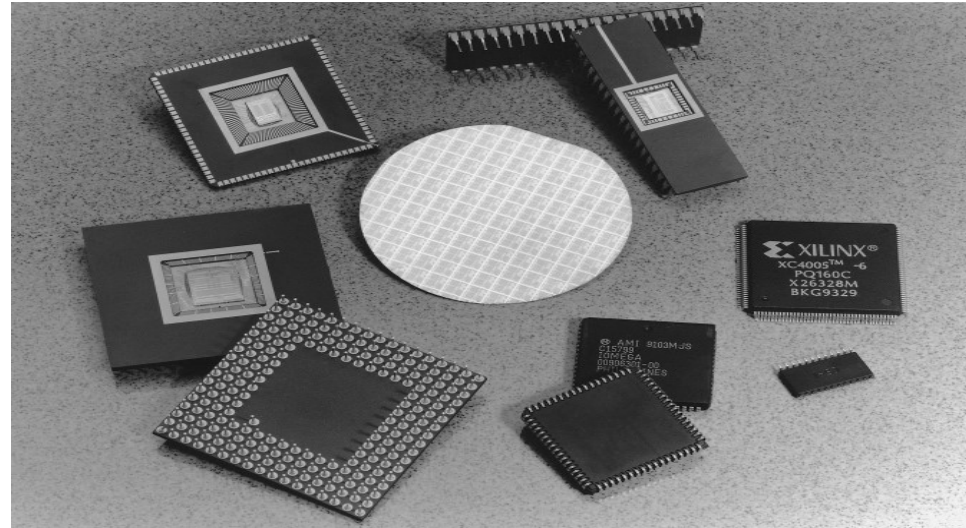
Metal 3  
Metal 2  
Metal 1  
Poly





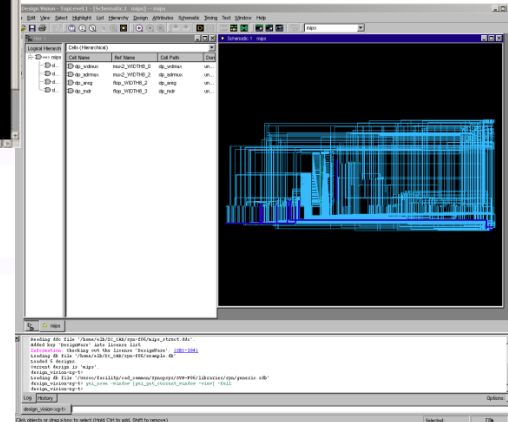
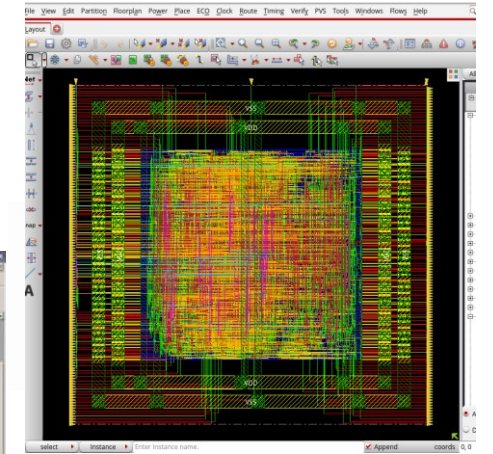
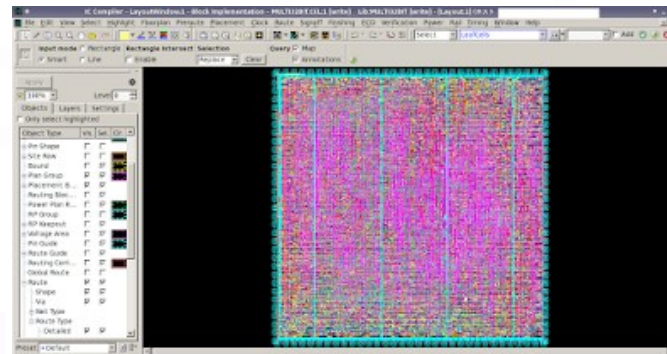
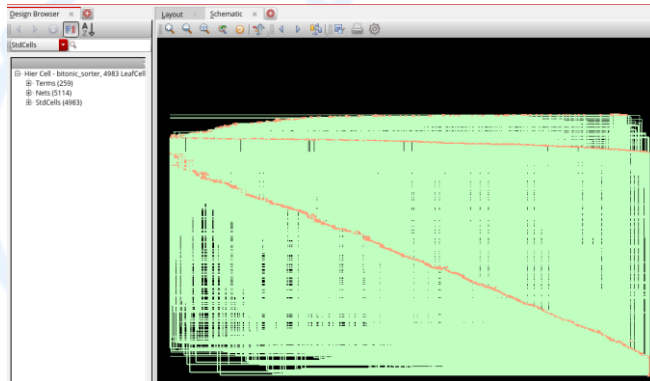
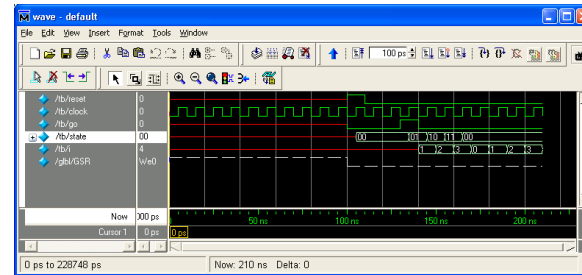
# IC Design Steps: IC Packaging

- Package is IC holder. It provides the physical, temperature and electrical protection.



# Electronic Design Automation (EDA) Tools

- Behavioural simulation
  - ModelSim, QuestaSim, Xcelium
- Logical Synthesis
  - Cadence Genus, Synopsys Design Compiler



- Physical synthesis (floorplanning/placement..../GDSII)
  - Cadence Encounter/Innovus, Synopsys IC Compiler
  - Signoff tools, Tempus/PrimeTime

Reference. Vazgen Melikyan, Synopsys University Courseware (Synopsys confidential information)  
<https://my.ece.utah.edu/~kstevens/5710/dc-soc.pdf>  
<https://web.mit.edu/6.111/www/labkit/simulation.shtml>

# Thanks



**Next Lecture: RTL-to-GDSII The Bare Minimum**